Technology Scaling and Roadmap for 22nm CMOS and beyond

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@Kyongpook National University

Hiroshi Iwai

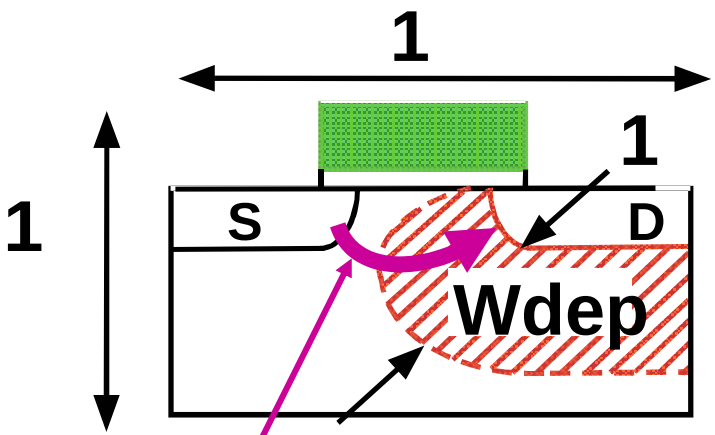
Tokyo Institute of Technology

Outline

1. Scaling
2. ITRS Roadmap
3. Voltage Scaling/ Low Power and Leakage
4. SRAM Cell Scaling
5. Roadmap for further future
   as a personal view

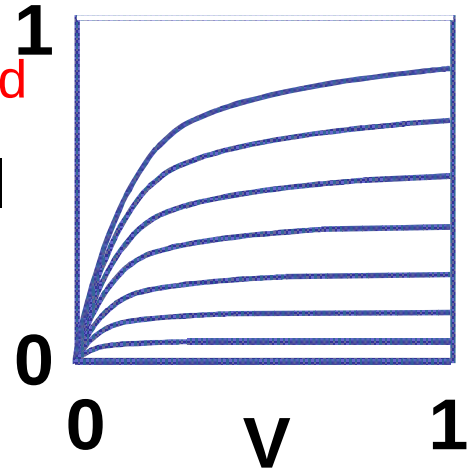
1. Scaling

Scaling Method: by R. Dennard in 1974



Wdep: Space Charge Region (or Depletion Region) Width

Wdep has to be suppressed
Otherwise, large leakage between S and D



Leakage current

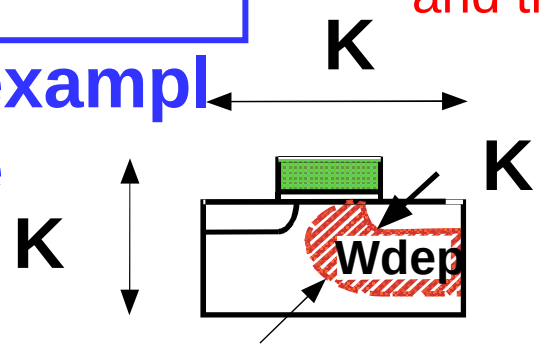
Potential in space charge region is high, and thus, electrons in source are attracted to the space charge region.

K=0.7 for example

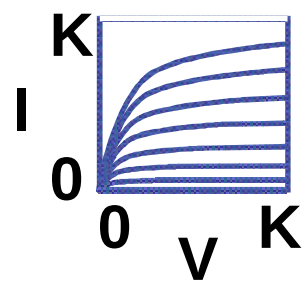
X, Y, Z : K, V : K, Na : 1/K

By the scaling, Wdep is suppressed in proportion, and thus, leakage can be suppressed.

→ Good scaled I-V characteristics



$$Wdep \propto \sqrt{V/Na} : K$$



I : K

Downscaling merit: Beautiful!

Geometry & Supply voltage	L_g, W_g T_{ox}, V_{dd}	K	**Scaling K : K=0.7 for example**
Drive current in saturation	I_d	K	$I_d = v_{sat} W_g C_o (V_g - V_{th})$ C_o: gate C per unit area → $W_g (t_{ox}^{-1})(V_g - V_{th}) = W_g t_{ox}^{-1}(V_g - V_{th}) = KK^{-1}K = K$
I_d per unit W_g	$I_d/\mu m$	1	I_d per unit $W_g = I_d / W_g = 1$
Gate capacitance	C_g	K	$C_g = \varepsilon_o \varepsilon_{ox} L_g W_g / t_{ox}$ → KK/K = K
Switching speed	τ	K	$\tau = C_g V_{dd} / I_d$ → KK/K = K
Clock frequency	f	1/K	$f = 1/\tau$ = 1/K
Chip area	A_{chip}	α	α: Scaling factor → **In the past, $\alpha>1$ for most cases**
Integration (# of Tr)	N	α/K^2	N → α/K^2 **= $1/K^2$, when $\alpha=1$**
Power per chip	P	α	$fNCV^2/2$ → $K^{-1}(\alpha K^{-2})K(K^1)^2 = \alpha$ **= 1, when $\alpha=1$**

k= 0.7 and α =1	k= 0.7^2 =0.5 and α =1
Single MOFET	
Vdd → 0.7 Lg → 0.7 Id → 0.7 Cg → 0.7	Vdd → 0.5 Lg → 0.5 Id → 0.5 Cg → 0.5
P (Power)/Clock → 0.7^3 = 0.34 τ (Switching time) → 0.7	P (Power)/Clock → 0.5^3 = 0.125 τ (Switching time) → 0.5
Chip	
N (# of Tr) → $1/0.7^2$ = 2 f (Clock) → 1/0.7 = 1.4 P (Power) → 1	N (# of Tr) → $1/0.5^2$ = 4 f (Clock) → 1/0.5 = 2 P (Power) → 1

- The concerns for limits of down-scaling have been announced for every generation.

- However, down-scaling of CMOS is still the 'royal road'* for high performance and low power.

- Effort for the down-scaling has to be continued by all means.

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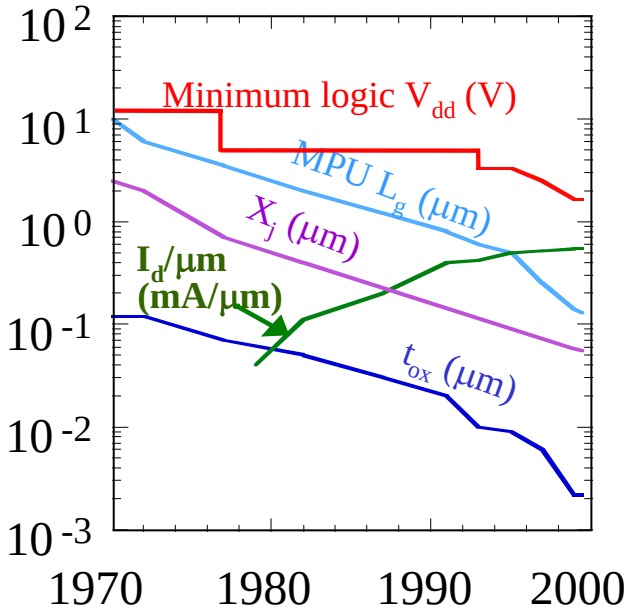
*Euclid of Alexandria (325BC?-265BC?)

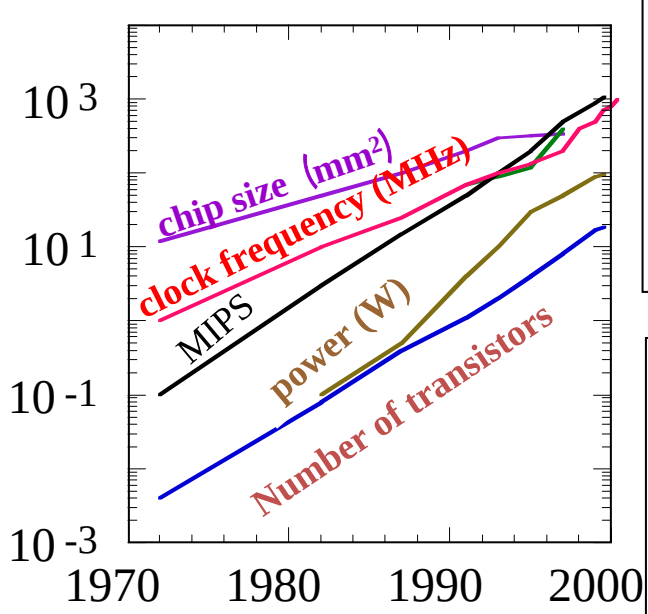
'There is no royal road to Geometry'

Mencius (Meng-zi), China (372BC?-289BC?)

孟子: 王道, 覇道 (Rule of right vs. Rule of military)

Actual past downscaling trend until year 2000





Past 30 years scaling

Merit: N, f increase

Demerit: P increase

V_{dd} scaling insufficient

⇩

Additional significant increase in I_d, f, P

Source. Iwai and S. Ohmi, Microelectronics Reliability 42 (2002), pp.1251-1268

Change in 30 years

	Ideal scaling	Real Change
L_g	K	10^{-2}
t_{ox}	K(10^{-2})	10^{-2}
V_{dd}	K(10^{-2})	10^{-1}
A_{chip}	α	10^{1}

	Ideal scaling	Real Change
I_d	K (10^{-2})	10^{-1}
I_d/μm	1	10^{1}
N	α/K^2(10^5)	10^{4}

	Ideal scaling	Real Change
f	1/K(10^2)	10^{3}
P = fαNCV^2	α(10^1)	10^{5}

Vd scaling insufficient, α increased → N, Id, f, P increased significantly

- Now, power and/or heat generation are the limiting factors of the down-scaling

- Supply voltage reduction is becoming difficult, because Vth cannot be decreased any more, as described later.

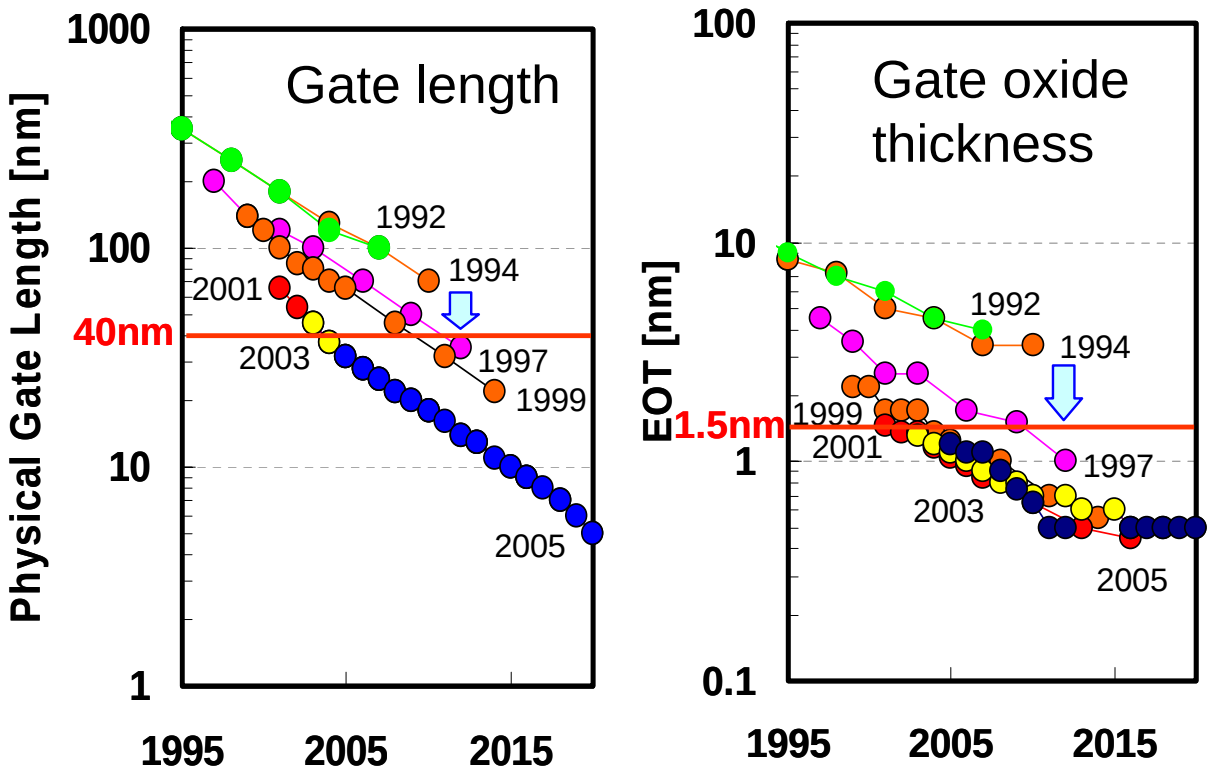
- Growth rate in clock frequency and chip area becomes smaller.

2. ITRS Roadmap
(for 22 nm CMOS logic)

What is a roadmap? What is ITRS?

Roadmap: Prediction of future technologies

ITRS: International Technology Roadmap for Semico
made by SIA (Semiconductor Industry Associatio
with Japan, Europe, Korea and Taiwan



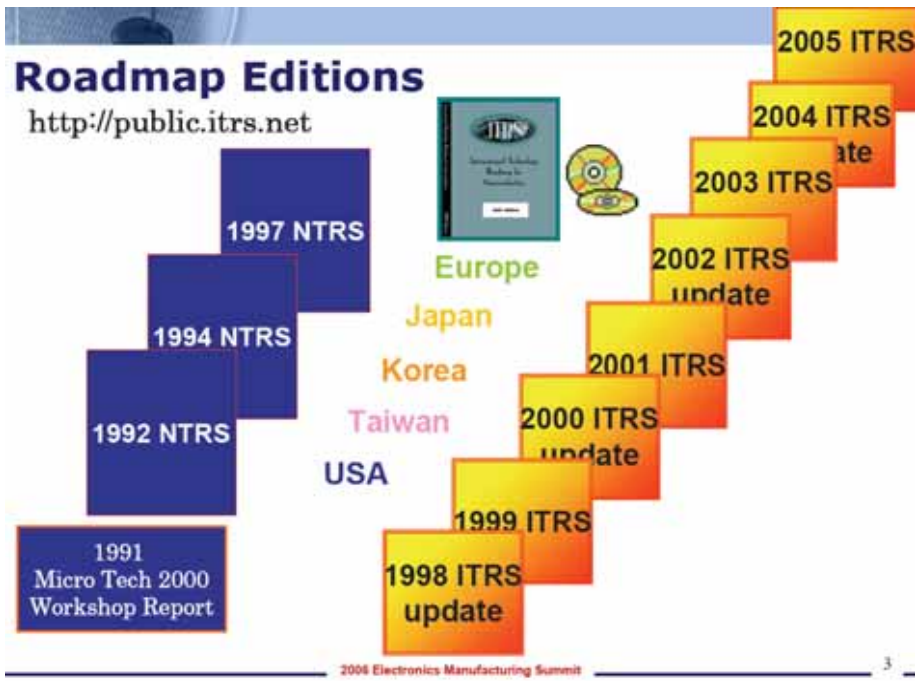
1992 -1997:NTRS (National Technology Roadmap)

1998 - : ITRS (International Technology Roadma

2008 ITRS update

2007 ITRS

2006 ITRS update

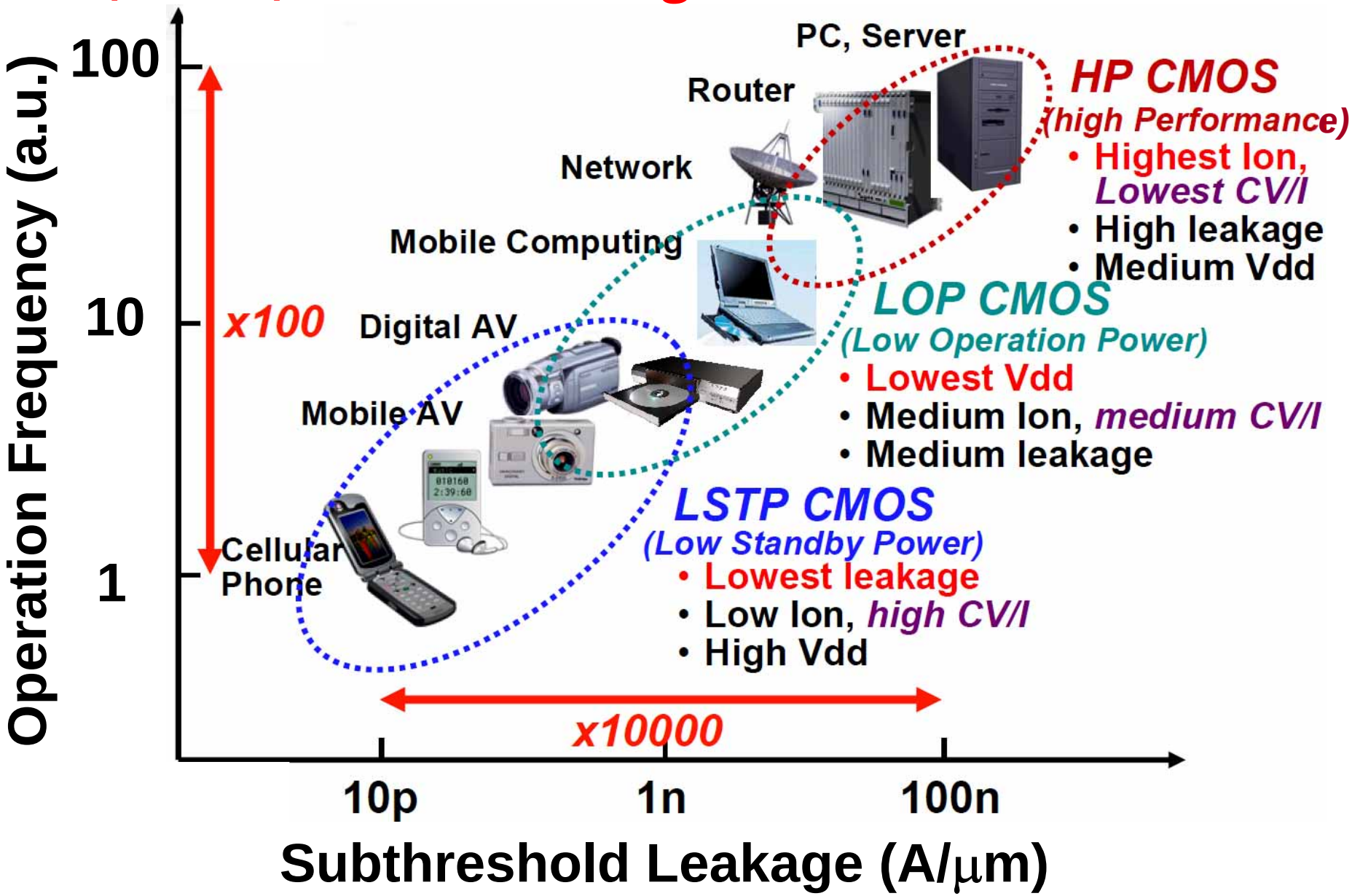


ITRS Roadmap does change every year!

2007 Edition	2003 Edition
2006 Update	2002 Update
2005 Edition	2001 Edition
2004 Update	2000 Update

http://www.itrs.net/reports.html

HP, LOP, LSTP for Logic CMOS



Source: 2007 ITRS Winter Public Conf.

What does '22 nm' mean in 22 nm CMOS Logic?

'XX nm CMOS Technology
Commercial Logic CMOS products

Technology name	Starting Year
45 nm	2007
32 nm	2009?
22 nm	2011?~ 2012?
16 nm	2013?~ 2014?

ITRS (Likely in 2008 Update)
for High Performance Logic

Year	Half Pitch (1st Metal)	Physical Gate Length
2007	68 nm	32 nm
2008	59 nm	29 nm
2009	52 nm	27 nm
2010	45 nm	24 nm
2011	40 nm	22 nm
2012	36 nm	20 nm
2013	32 nm	18 nm
2014	29 nm	16 nm

Source: 2008 ITRS Summer Public Conf.

'XX nm' CMOS Logic Technology:

- In general, there is no common corresponding parameter with 'XX nm' in ITRS table, which stands for 'XX nm' CMOS.

What does ‘22 nm’ mean in 22 nm CMOS Logic?

-‘ XX nm’ does not correspond to the ‘Half Pitch’ nor ‘Physical Gate Length’ of ITRS.

-‘XX nm’ is now just a commercial name for CMOS Logic generation of size and its technology.

- Actual parameter values and starting years for commercial products are somewhat different from the above ITRS table, depending on semiconductor companies.

- In 22 and 16 nm technologies, physical gate lengths of high-performance logic device may be close to XX nm.

What does ‘22 nm’ mean in 22 nm CMOS Logic?

8μm → 6μm → 4μm → 3μm → 2μm → 1.2μm → 0.8μm → 0.5μm

- Originally, ‘XX’ means lithography resolution.
- Thus, ‘XX’ was the gate length, and half pitch of lines
- ‘XX’ had shrunk 0.7 in 3 years in average (0.5 in 6 years) those days.
- ‘XX’ value deviated among companies: example:**1.5μm, 1.2μm, 1μm**

→ 350nm → 250nm → 180nm → 130nm → 90nm → 65nm → 45nm

-‘XX’ values were established by NTRS* and ITRS with the term of ‘Technology Node**’ and ‘Cycle***’ using typical ‘half pitch value’.

*NTRS: National Tech. Roadmap, **Term ‘Technology Node’ is not used now.
***Cycle: Period or year for which the half pitch becomes X0.71.

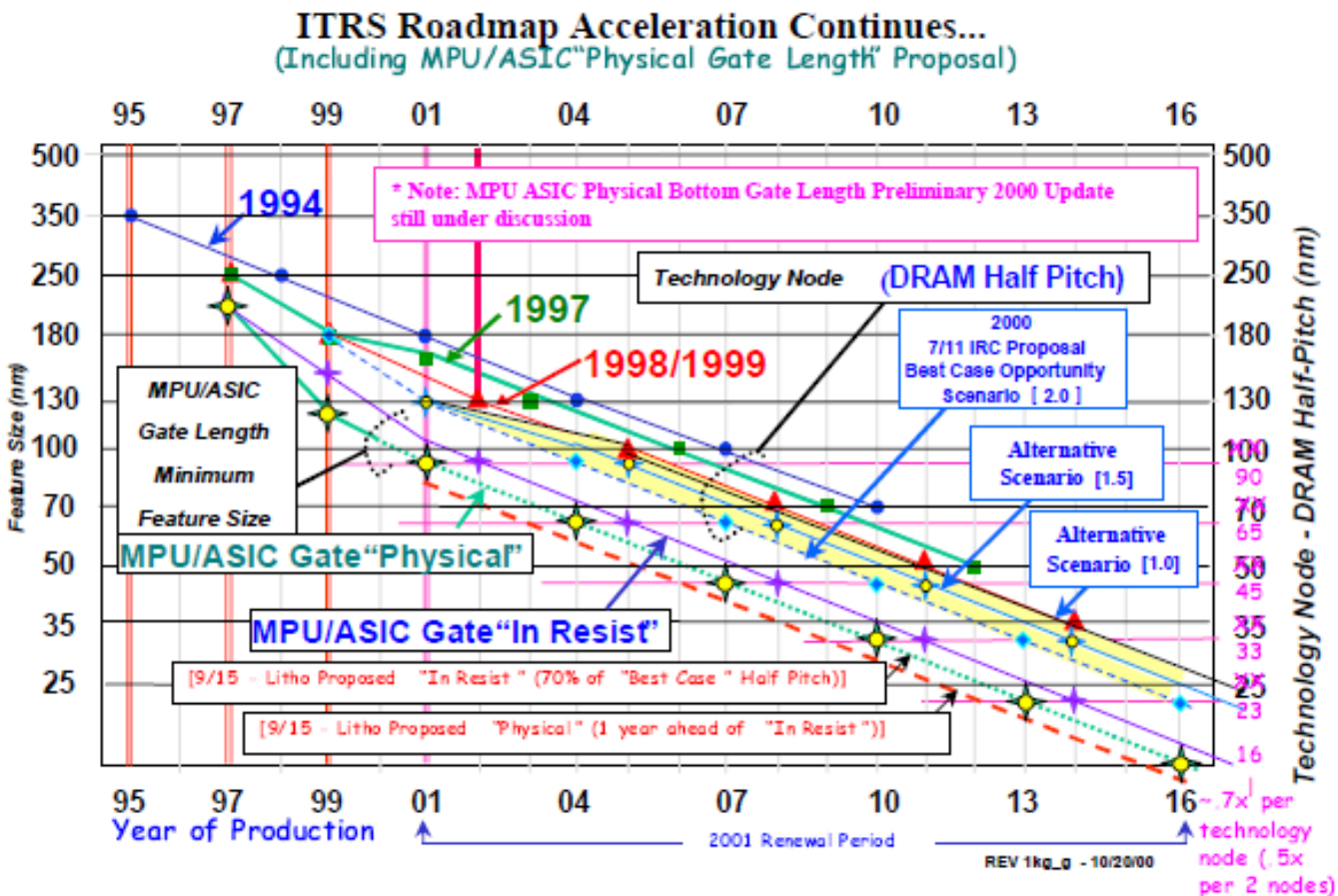
- The gate length of logic CMOS became smaller with one or two generations from the half pitch, and ‘XX’ names ahead of generations have been used for logic CMOS.

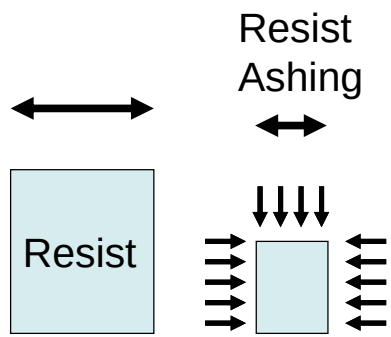
- Memory still keeps the half pitch as the value of ‘XX’

→ 32nm → 22nm → 16nm → 11nm → 8nm?? → 5.5nm ??

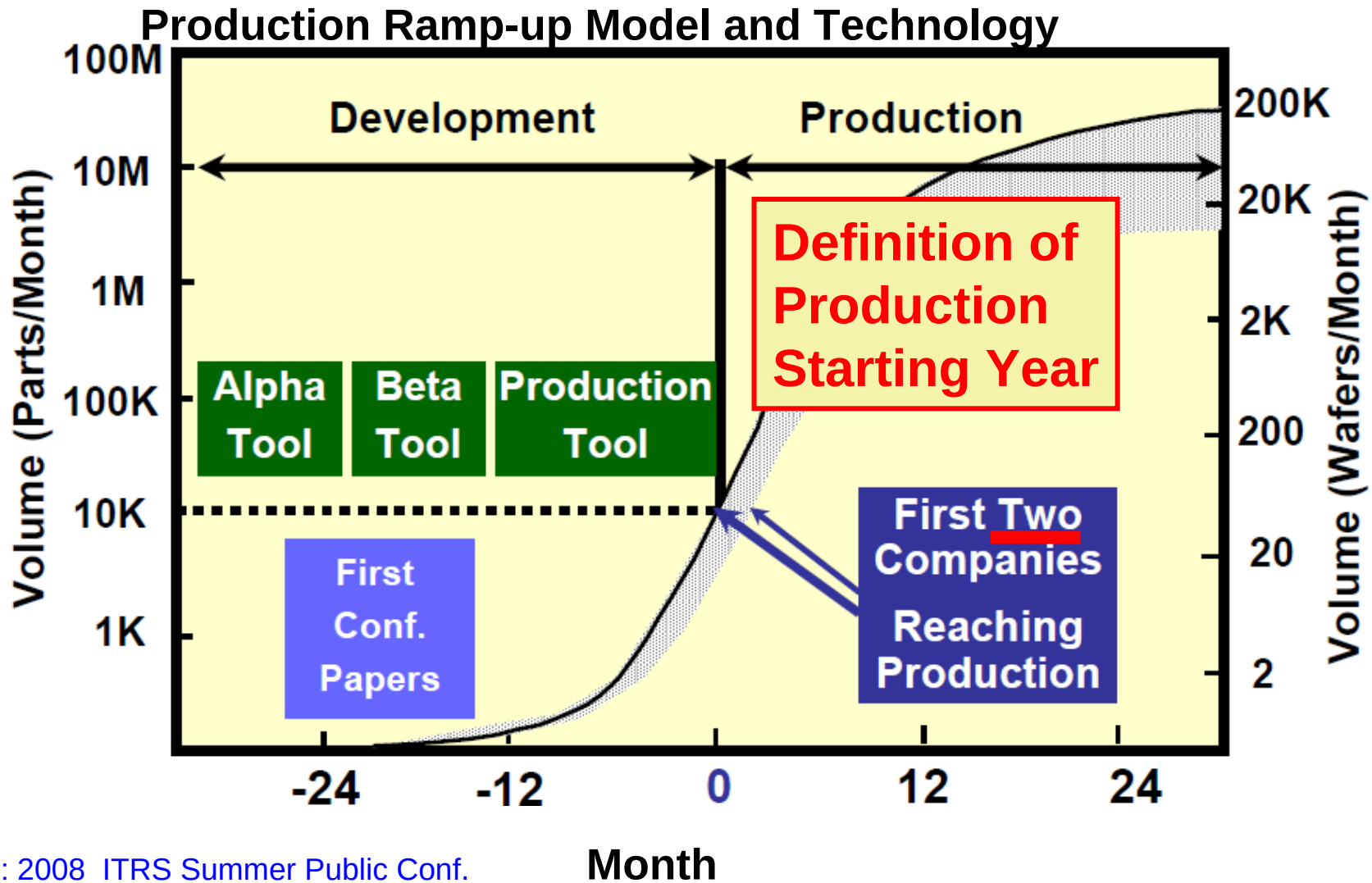
What does ‘22 nm’ mean in 22 nm CMOS Logic?

Gate length of Logic CMOS became significantly smaller than lithography resolution or half-pitch using special technique such as resist aching (or trimming) method since 350 nm CMOS.





Source: ITRS 2001 Update



Source: 2008 ITRS Summer Public Conf.

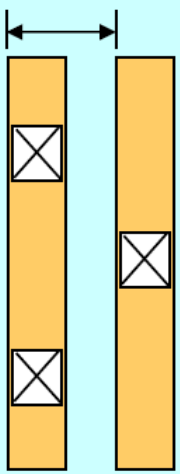
Some Problem: Number of most advanced logic CMOS companies is decreasing in generations.

Definition of the Half Pitch

Logic 1st Metal Half Pitch

DRAM ½ Pitch
= DRAM Metal Pitch/2
MPU/ASIC M1 ½ Pitch
= MPU/ASIC M1 Pitch/2

Metal
Pitch

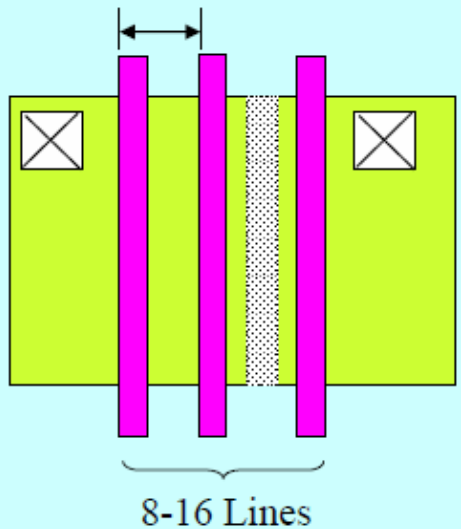


Typical DRAM/MPU/ASIC
Metal Bit Line

Flash Poly Gate Half Pitch

FLASH Poly Silicon ½ Pitch
= Flash Poly Pitch/2

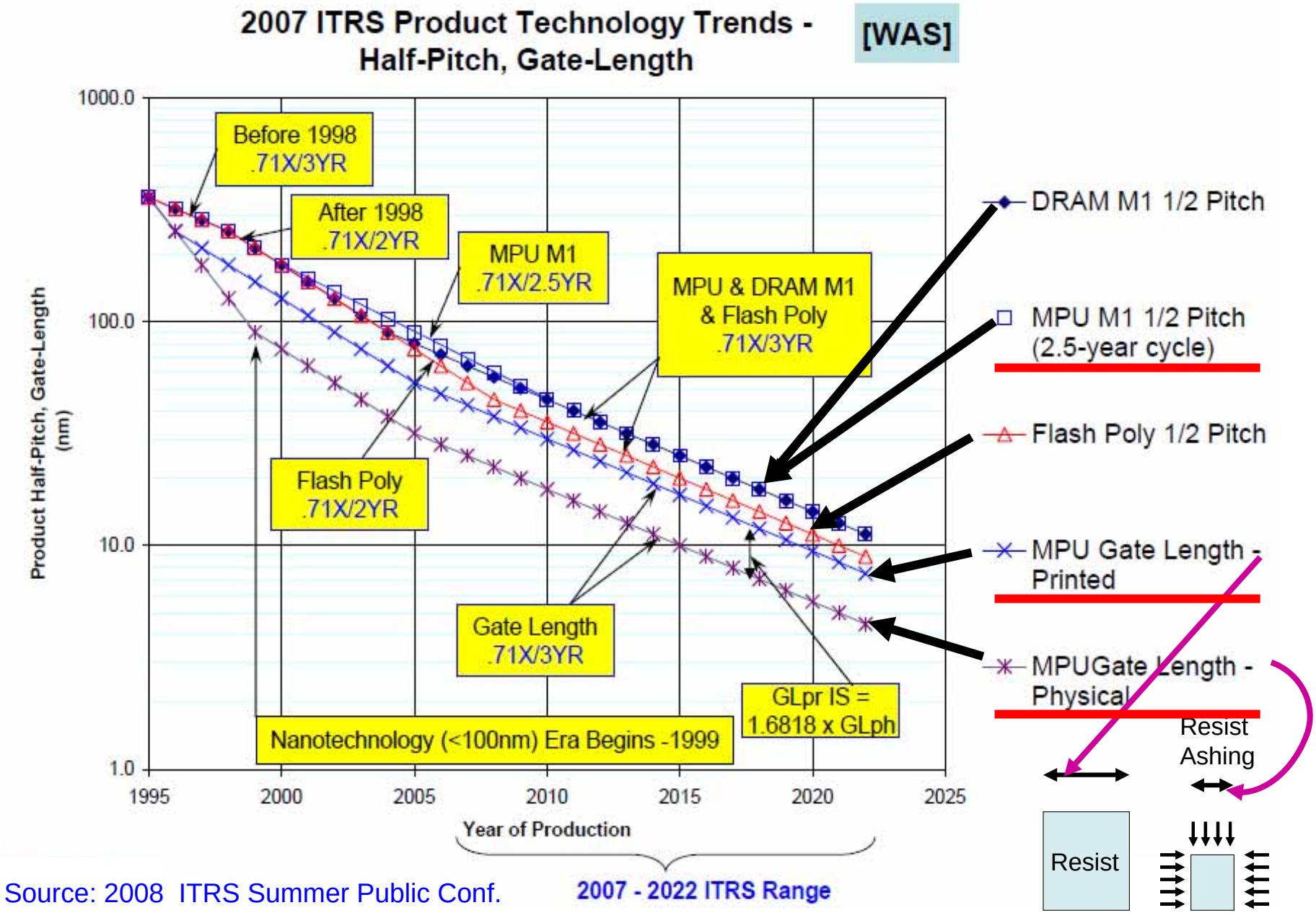
Poly
Pitch



Typical flash
Un-contacted Poly

Source: 2008 ITRS Summer Public Conf.

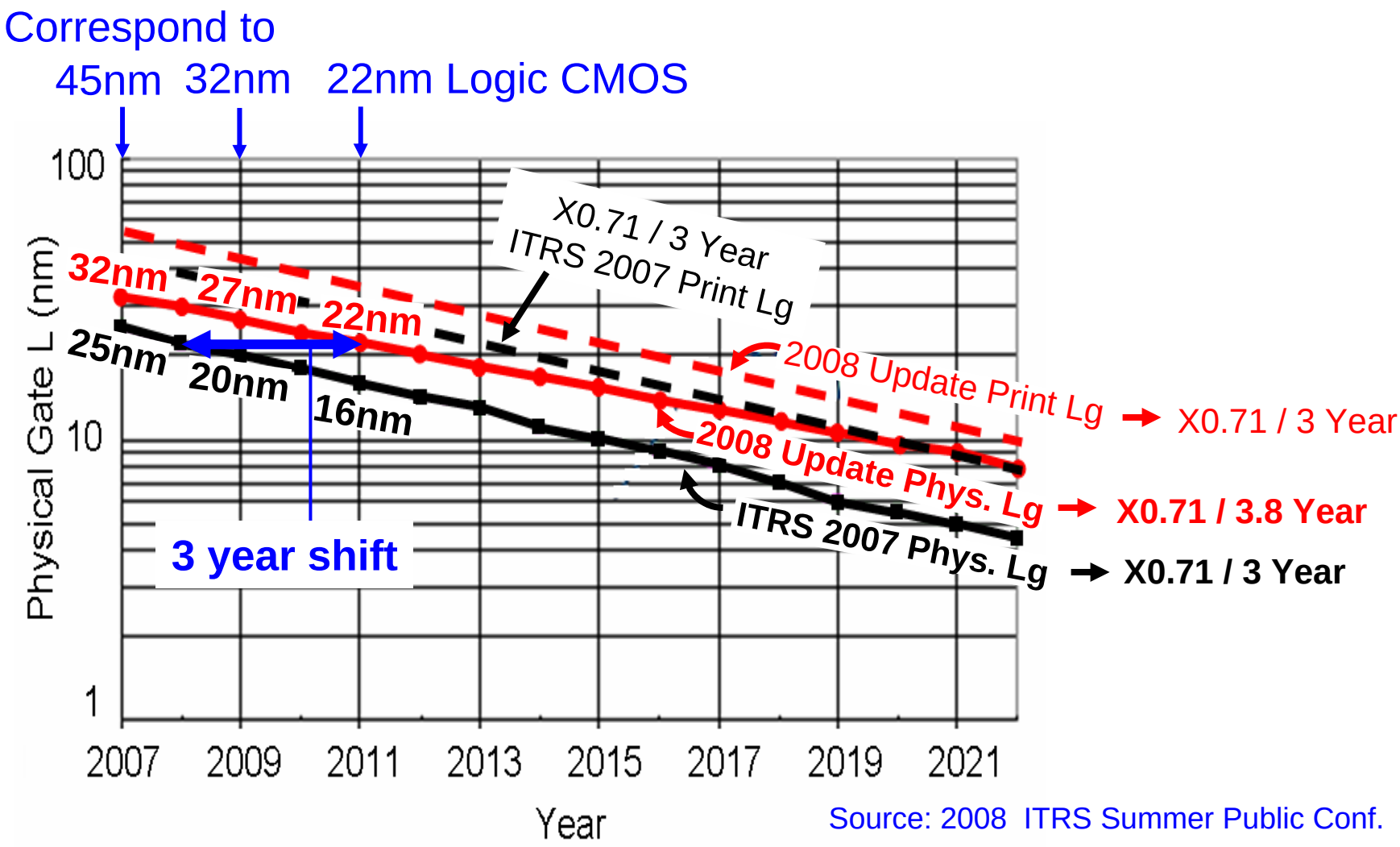
For example, Typical Half Pitches at ITRS 2007



Source: 2008 ITRS Summer Public Conf.

Physical gate length in past ITRS was too aggressive.
The dissociation from commercial product prediction will be adjusted.

Physical gate length of High-Performance logic will shift by 3-5 yrs.



Source: 2008 ITRS Summer Public Conf.

EOT and Xj shift backward, corresponding to Lg shift

EOT: 0.55 nm → 0.88 nm, Xj: 8 nm → 11 nm @ 22nm CMOS

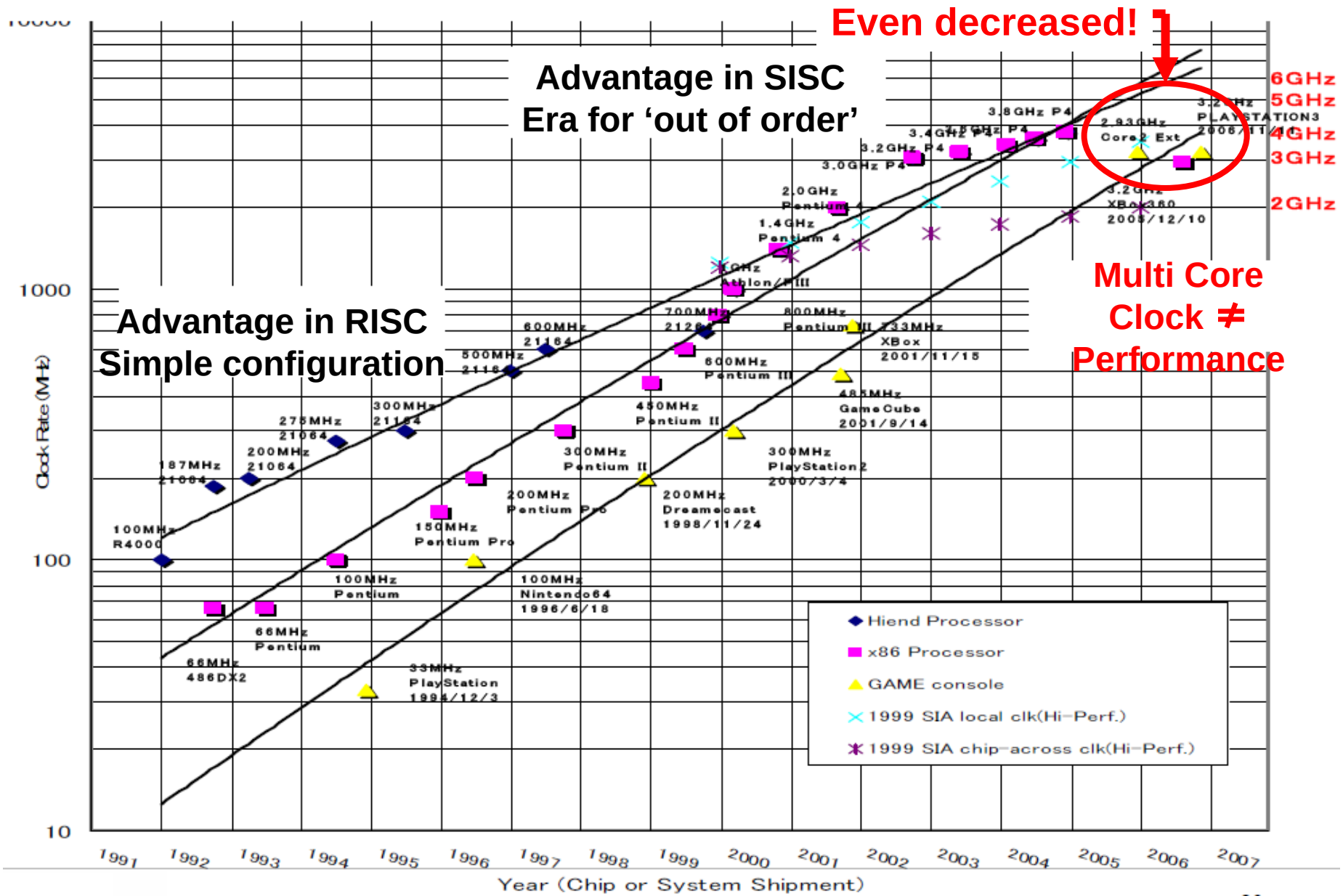
Likely in 2008 Update **Correspond to 22nm** Source: 2008/ ITRS Summer Public Conf.

Year of Production	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017	2018	2019	2020	2021	2022
2007 MPU/ASIC Lg (nm)	25	23	20	18	16	14	13	11	10	9	8	7	6.3	5.6	5	4.5
2008 MPU/ASIC Lg (nm)	32	29	27	24	22	20	18	17	15	14.0	12.8	11.7	10.7	9.7	8.9	8.1
Shift/Interpolate Formua	2005	intrp	intrp	intrp	intrp	2009	2010	intrp	intrp	2012	intrp	intrp	intrp	intrp	intrp	intrp
EOT w/3E20 poly, bulk MPU (nm)	1.2	0.71	0.54	0.41												
EOT w/3E20 poly, bulk MPU (nm)	1.3	1.2	1.2	1	0.68	0.54	0.41				Likely in 2008 Update					
EOT w/metal gate, bulk MPU (nm)		0.9	0.75	0.65	0.55	0.50										
EOT w/metal gate, bulk MPU (nm)			1.0	0.95	0.88	0.75	0.65	0.60	0.53	0.5	Likely in 2008 Update					
Drain Ext. X_j bulk MPU (nm)	12.5	11	10	9	8	7										
Drain Ext. X_j bulk MPU (nm)	11	11	11	11	11		9	8.5	7.7	7	Likely in 2008 Update					

non-steady trend corrected

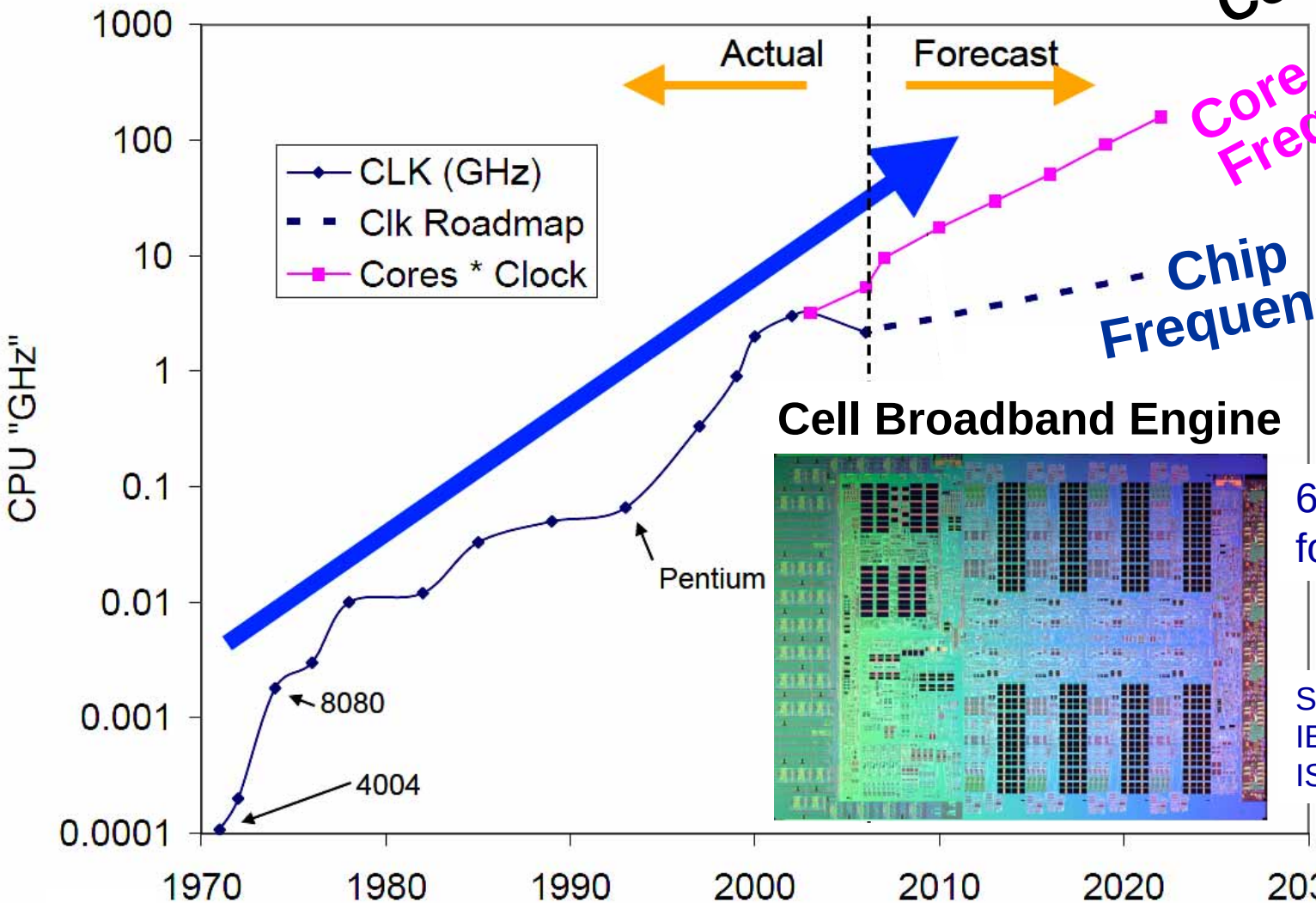
filled in for metal gate EOT for 2009/10 based on latest conference presentations

Clock frequency does not increase aggressively anymore.



Source: Mitsuo Saito, Toshiba

MPU "GHz" by "Cores" ITRS2007



Continued?

Core Clock Frequency

Chip Frequency

Cell Broadband Engine

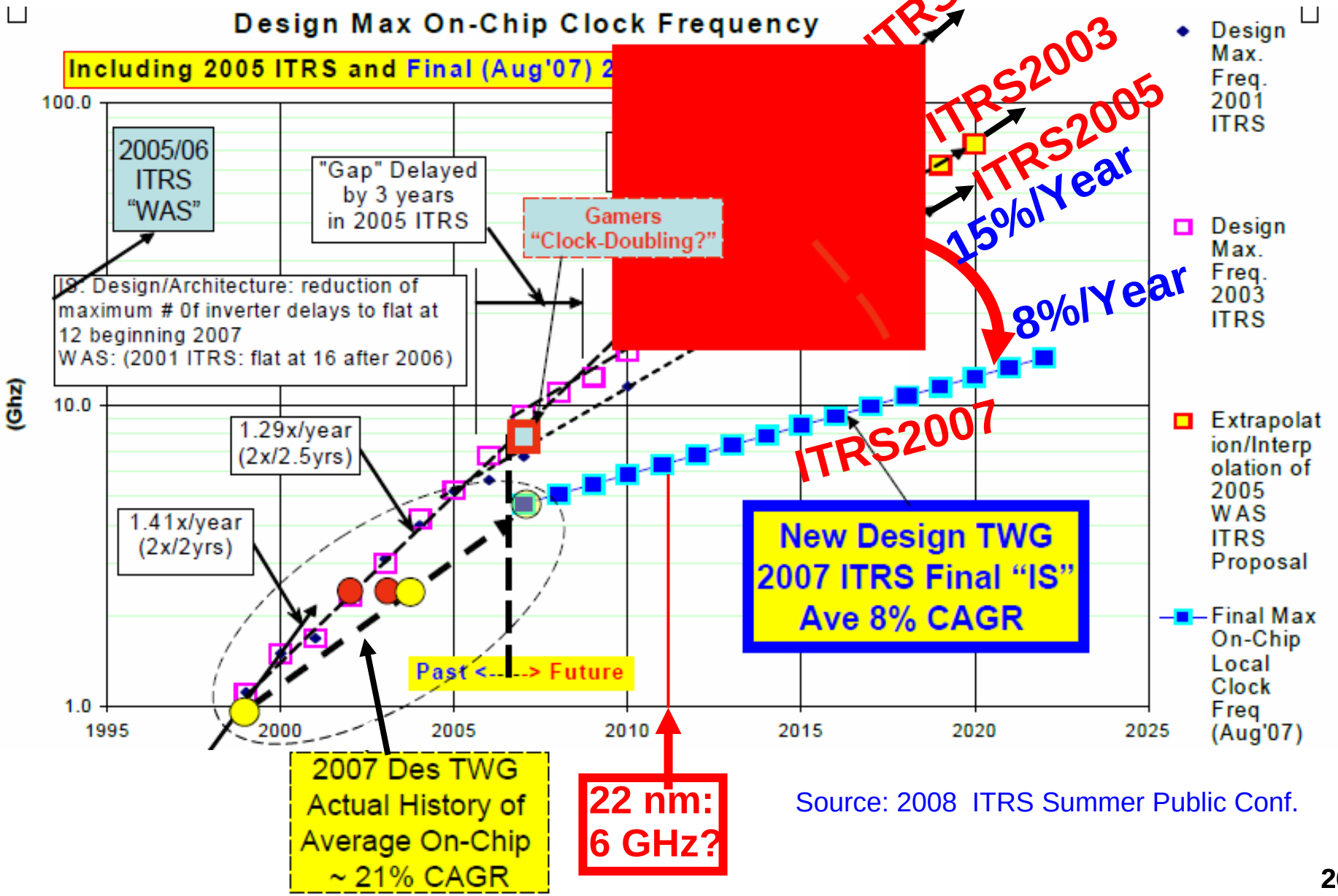
6GHz capability for SRAM

Source:
IBM, Toshiba, Sony
ISSCC2008 and 08

Source: 2007 ITRS Winter Public Conf.

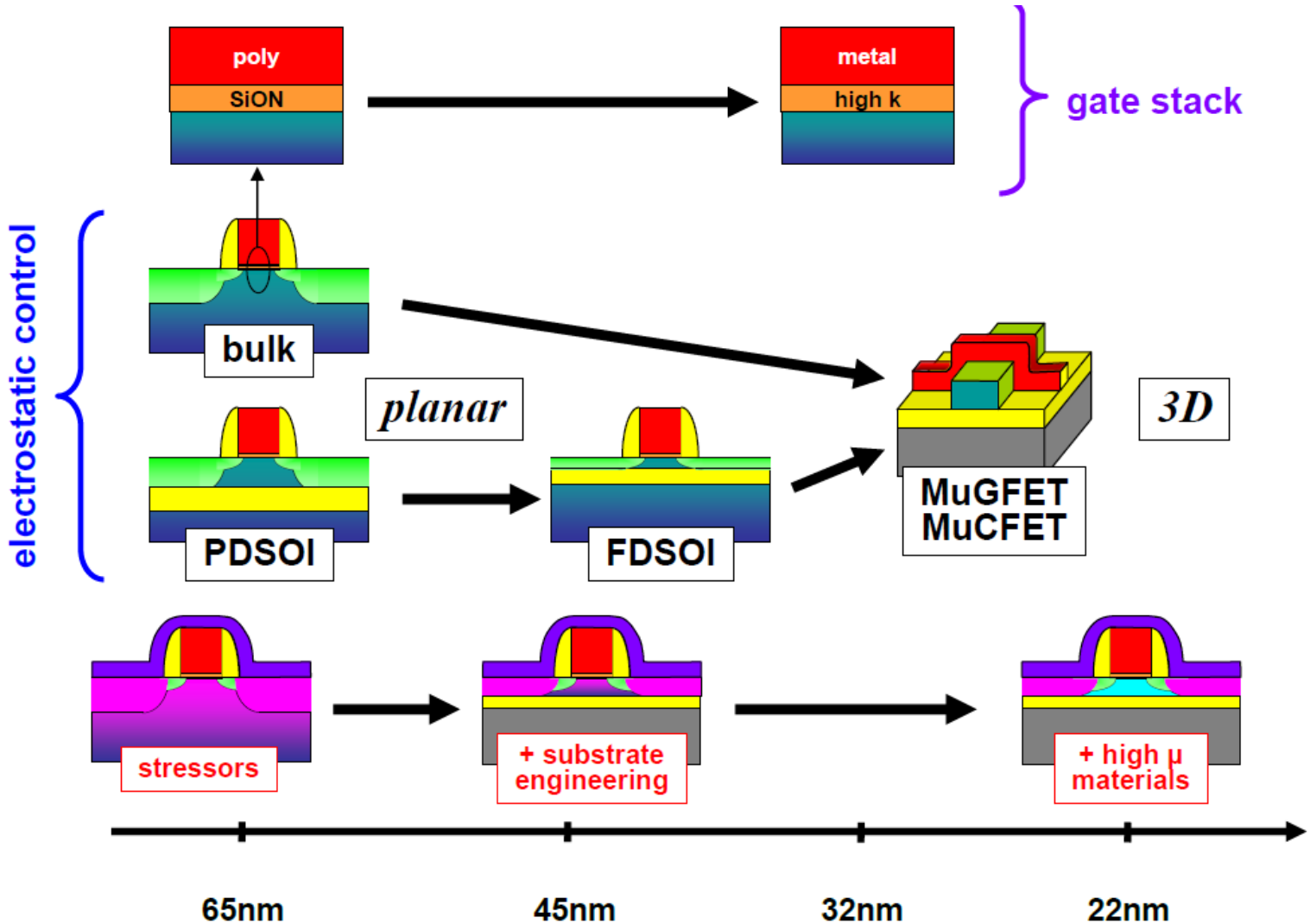
Clock frequency Change in the past ITRS

(Max on chip frequency or 'Core clock')



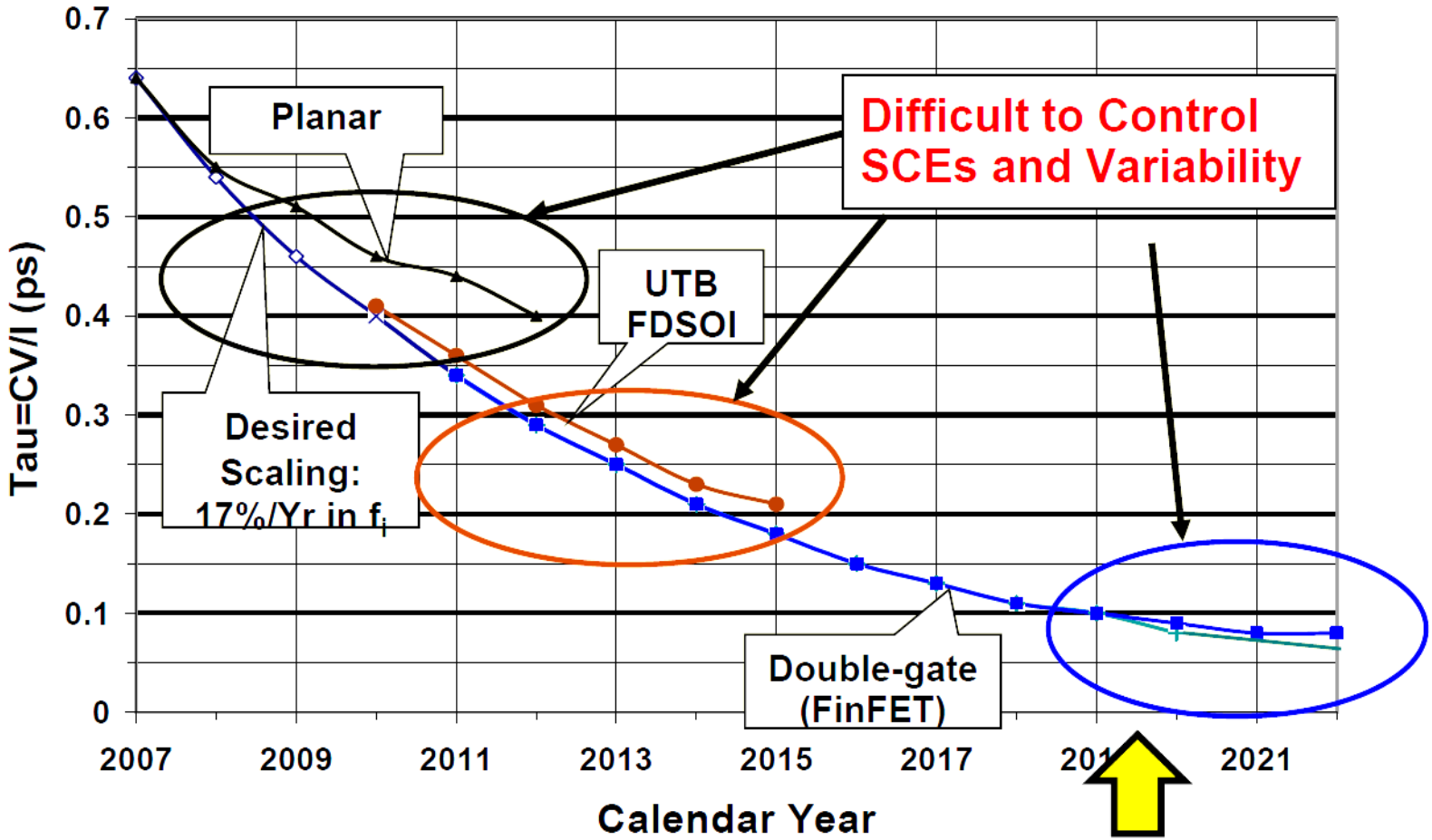
Source: 2008 ITRS Summer Public Conf.

Structure and technology innovation (ITRS 2007)



Source: 2008 ITRS Summer Public Conf.

Technology innovation described in ITRS 2007

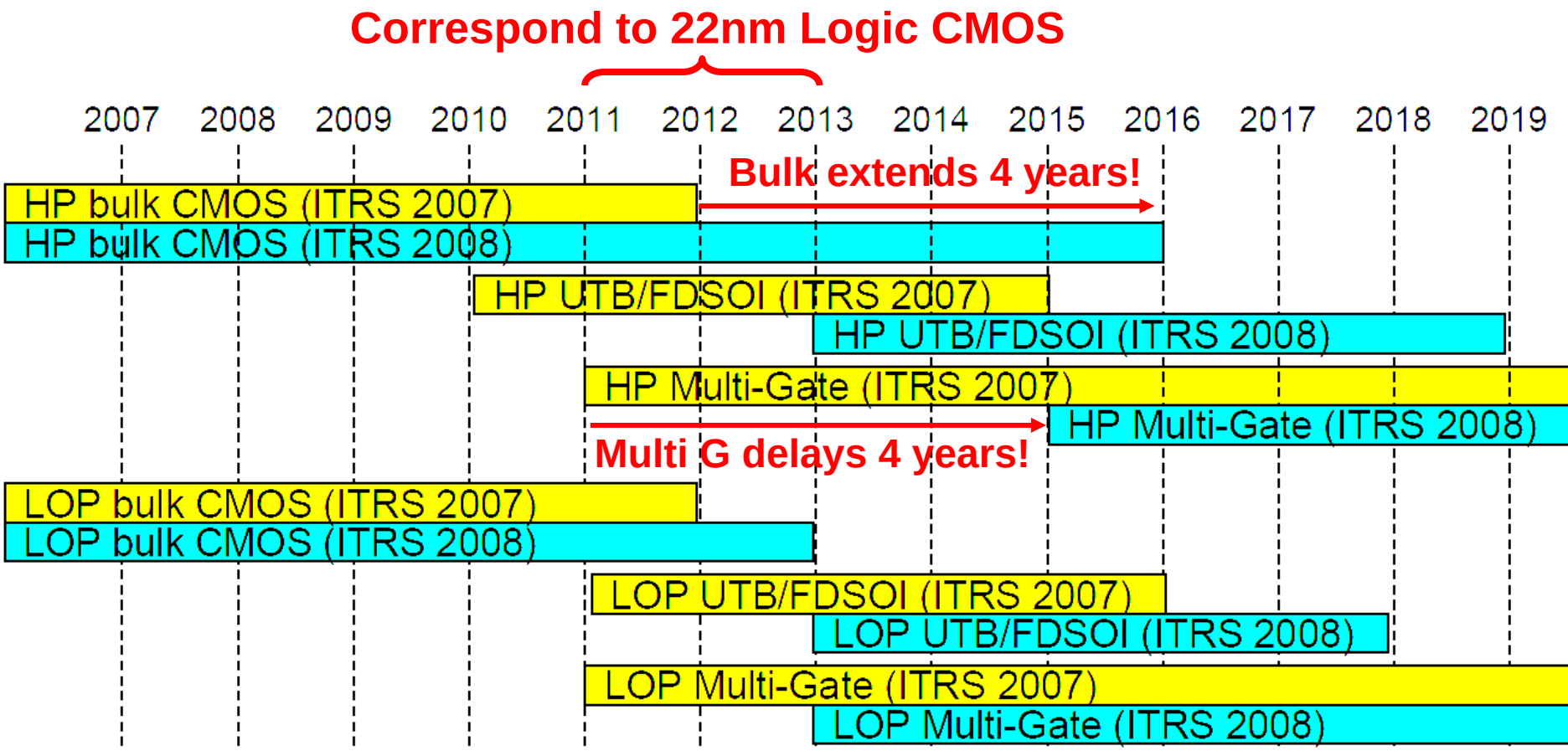


Alternative material (Ge, III-V) and structure (Nanowire) in channel region.

Source: 2007 ITRS Winter Public Conf.

Timing of CMOS innovations shifts backward.

Bulk CMOS has longer life now!



Source: 2008 ITRS Summer Public Conf.

Wafer size (ITRS 2007)

Correspond to 22nm

Year of Production	*2007*	*2008*	*2009*	*2010*	*2011*	*2012*	*2013*	*2014*	*2015*
MPU/ASIC Metal 1 (M1) ½ Pitch (nm)(contacted)	*68*	*59*	*52*	*45*	*40*	*36*	*32*	*28*	*25*
MPU Physical Gate Length (nm)	*25*	*23*	*20*	*18*	*16*	*14*	*13*	*11*	*10*
MPU High-Performance Total Chip Area(mm^2)	*310*	*246*	*195*	*310*	*246*	*195*	*310*	*246*	*195*
MPU High-Performance Active Transistor Area(mm^2)	*31.7*	*25.1*	*20.0*	*31.7*	*25.1*	*20.0*	*31.7*	*25.1*	*20.0*
*General Characteristics * (99% Chip Yield)*									
Maximum Substrate Diameter (mm)—High-volume Production (>20K wafer starts per month)**	300	300	300	300	300	450	450	450	450

Source: ITRS 2007

→ ??

Maybe delay??

Gate CD (Critical Dimension) Control

ITRS 2007

Correspond to 22nm Logic

Year of Production	2007	2008	2009	2010	2011	2012	2013	2014	2015
MPU/ASIC Metal 1 (M1) ½ Pitch (nm)(contacted)	68	59	52	45	40	36	32	28	25
MPU Physical Gate Length (nm)	25	23	20	18	16	14	13	11	10
Total maximum allowable etch 3σ (nm), including photoresist trim and gate etch [AA]	1.5	1.38	1.2	1.08	0.96	0.84	0.78	0.66	0.6

Source: ITRS 2007

2008 Update

Correspond to 22nm Logic

Year of Production	2007	2008	2009	2010	2011	2012	2013	2014	2015
MPU Physical Gate Length (nm)	32	29	27	24	22	20	18	17	15
L_{gate} 3 σ variation (nm) [Z]	3.82	3.49	3.18	2.9	2.65	2.42	2.21	2.02	1.84

Source: 2008 ITRS Summer Public Conf.

Gate CD control color changed to 'white' through 2011 and to 'yellow' for 2012 reflecting the new Lg scaling

ITRS2008 Low-k Roadmap Update

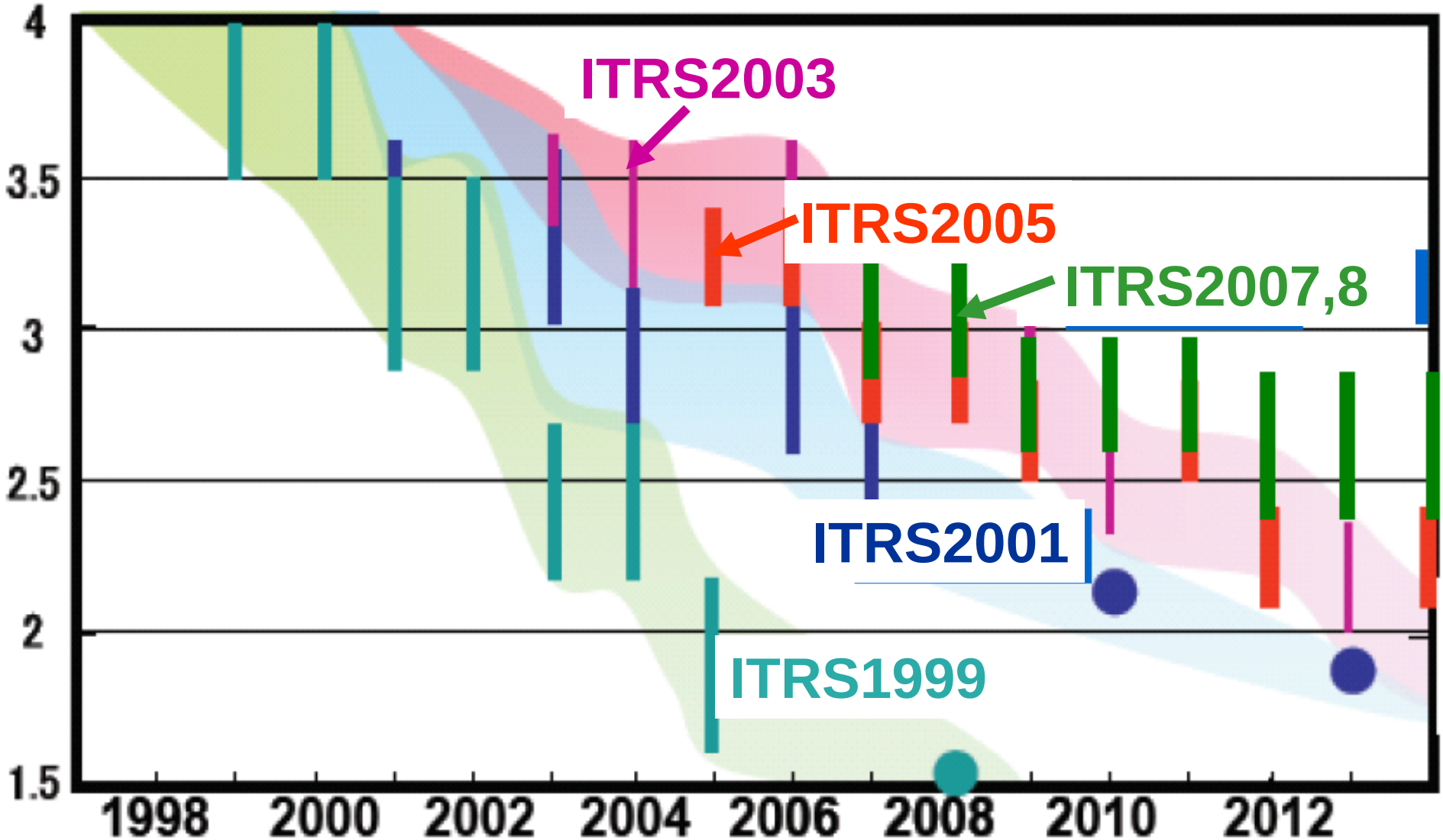
Correspond to 22nm Logic

		Near-term					
ITRS 2007	*Year of Production*	*2008*	*2009*	*2010*	*2011*	*2012*	*2013*
	Interlevel metal insulator – effective dielectric constant (κ)	2.7-3.0	2.5-2.8	2.5-2.8	2.5-2.8	2.1-2.4	2.1-2.4
Update 2008	Interlevel metal insulator – effective dielectric constant (κ)	2.9-3.3	2.6-2.9	2.6-2.9	2.6-2.9	2.4-2.8	2.4-2.8
ITRS 2007	Interlevel metal insulator – bulk dielectric constant (κ)	2.3-2.7	2.1-2.4	2.1-2.4	2.1-2.4	1.8-2.1	1.8-2.1
Update 2007	Interlevel metal insulator – bulk dielectric constant (κ)	2.5-2.8	2.3-2.6	2.3-2.6	2.3-2.6	2.1-2.4	2.1-2.4

Source: 2008 ITRS Summer Public Conf.

k value increases by 0.1 ~ 0.3

Historical Transition of ITRS Low-k Roadmap



Source: 2008 ITRS Summer Public Conf.

Roadmap towards 22nm technology and beyond

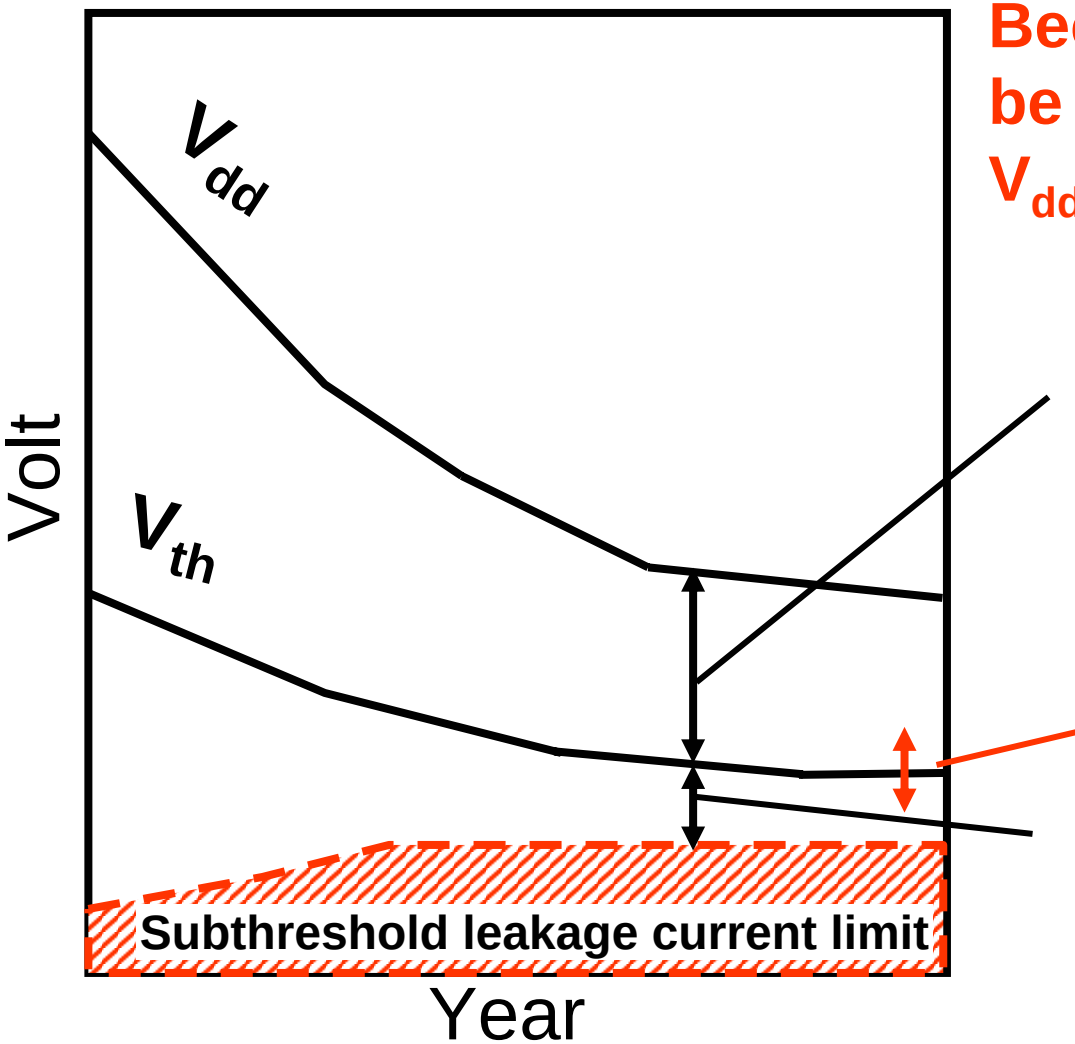
- Physical gate length downsizing rate will be less aggressive.

- Corresponding to the above, performance increase would slow down – Clock frequency, etc.

- Introduction of innovative structures – UTB SOI and DG delayed, and bulk CMOS has longer life than predicted by previous ITRS roadmaps.

3. Voltage Scaling / Low Power and Leakage

Difficulty in Down-scaling of Supply Voltage: Vdd



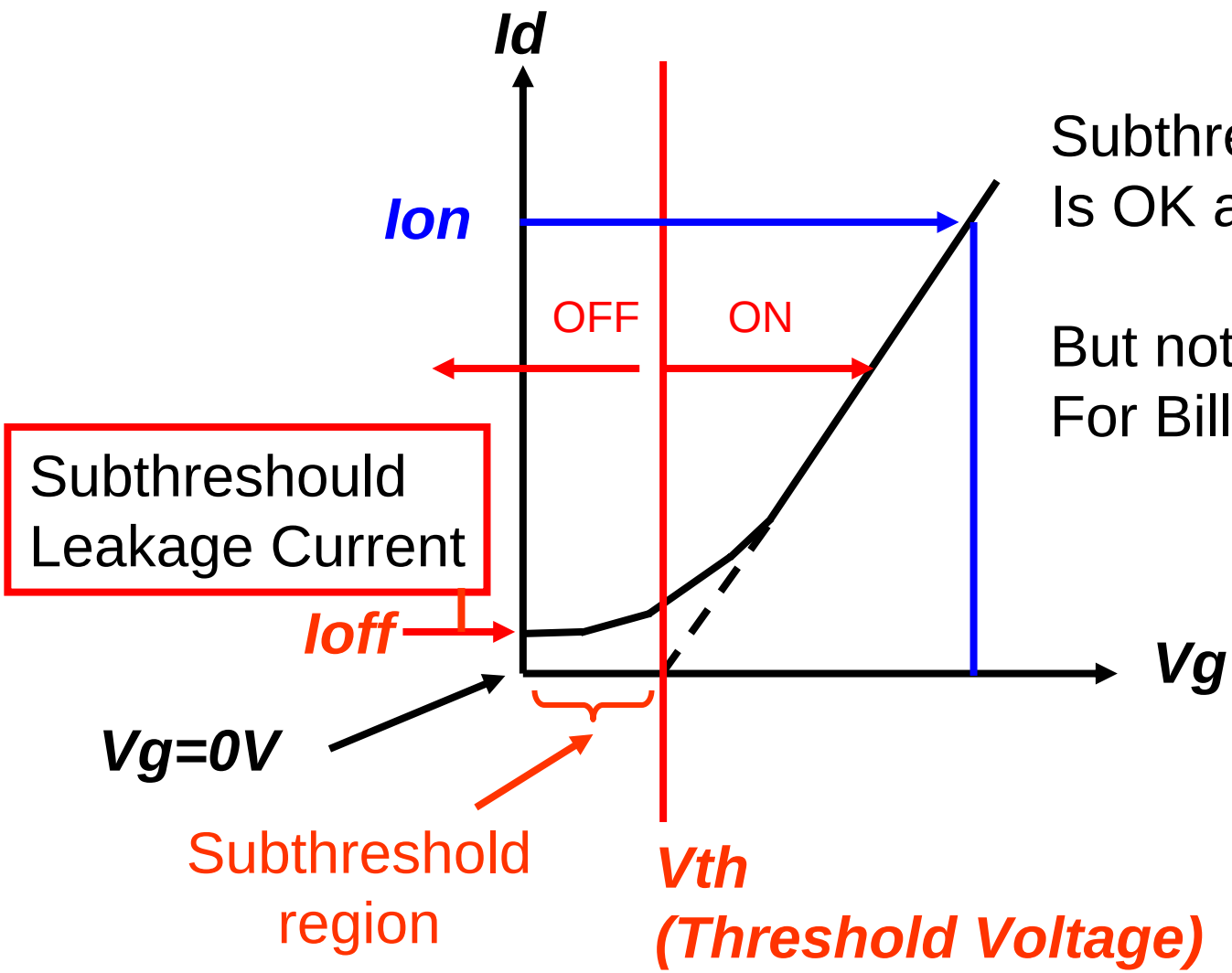
Because, V_{th} cannot be down-scaled anymore, V_{dd} down-scaling is difficult.

$V_{dd} - V_{th}$ determines the performance (High Id) and cannot be too small.

ΔV_{th}: V_{th} variation

$> \Delta V_{th}$
Margin for V_{th} variation is necessary

Subtheshold leakage current of MOSFET



Subthreshold Current
Is OK at Single Tr. level

But not OK
For Billions of Trs.

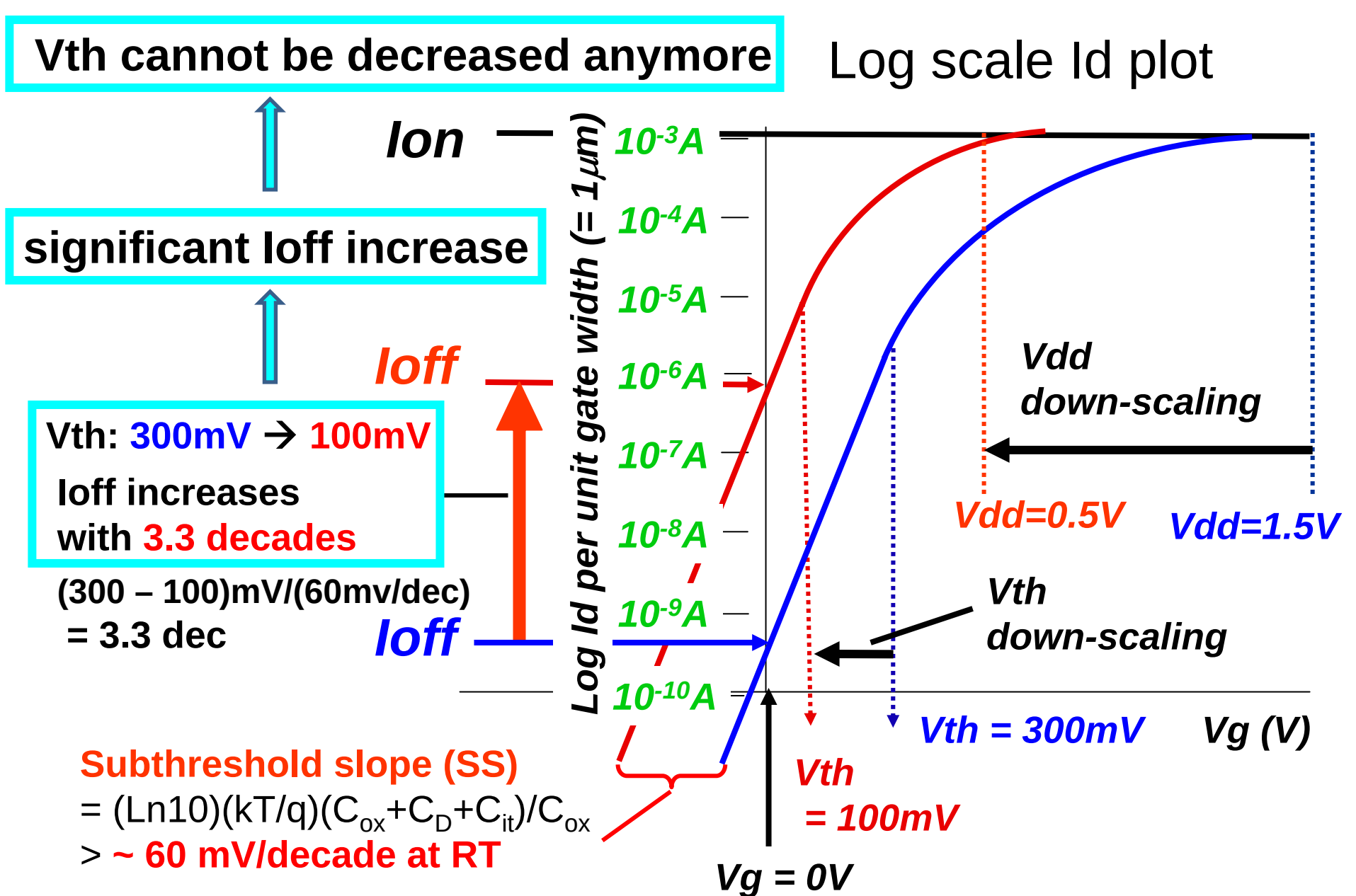
Vth cannot be decreased anymore

significant Ioff increase

Vth: 300mV → 100mV

Ioff increases with 3.3 decades

(300 – 100)mV/(60mv/dec) = 3.3 dec



Subthreshold slope (SS)

$= (Ln10)(kT/q)(C_{ox}+C_D+C_{it})/C_{ox}$

> **~ 60 mV/decade at RT**

SS value:

Constant and does not become small with down-scaling

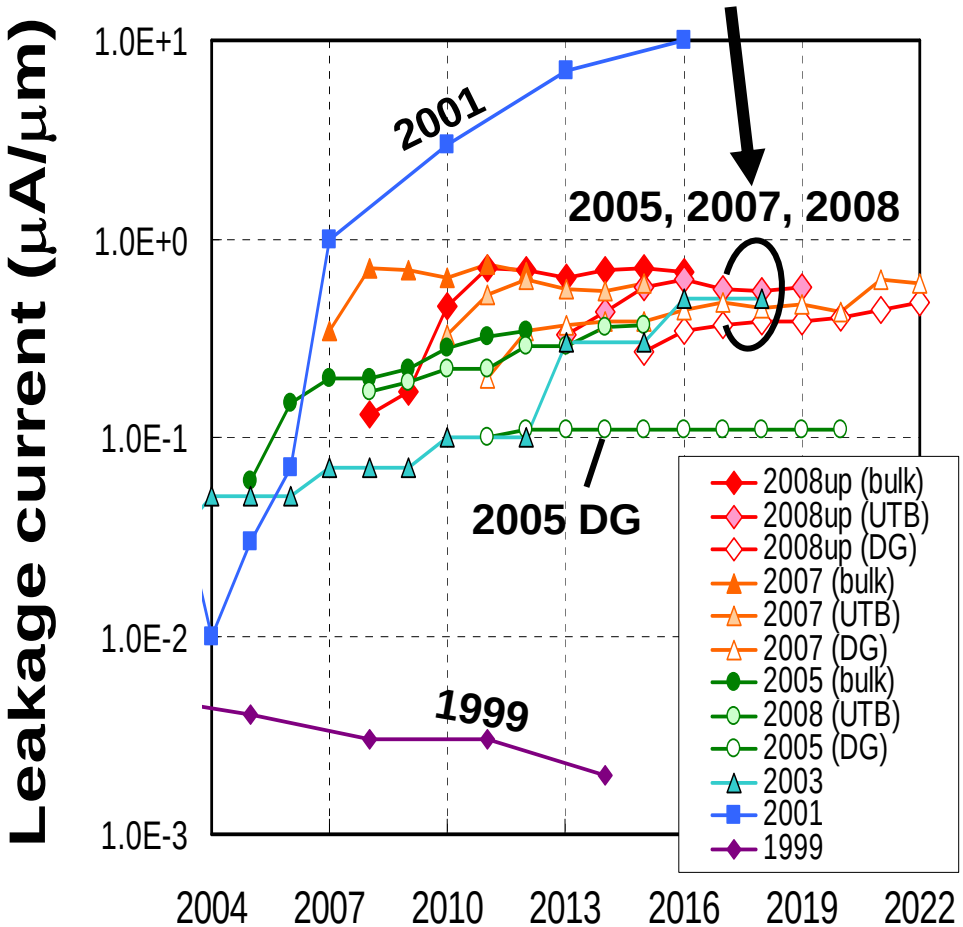
ITRS for HP logic

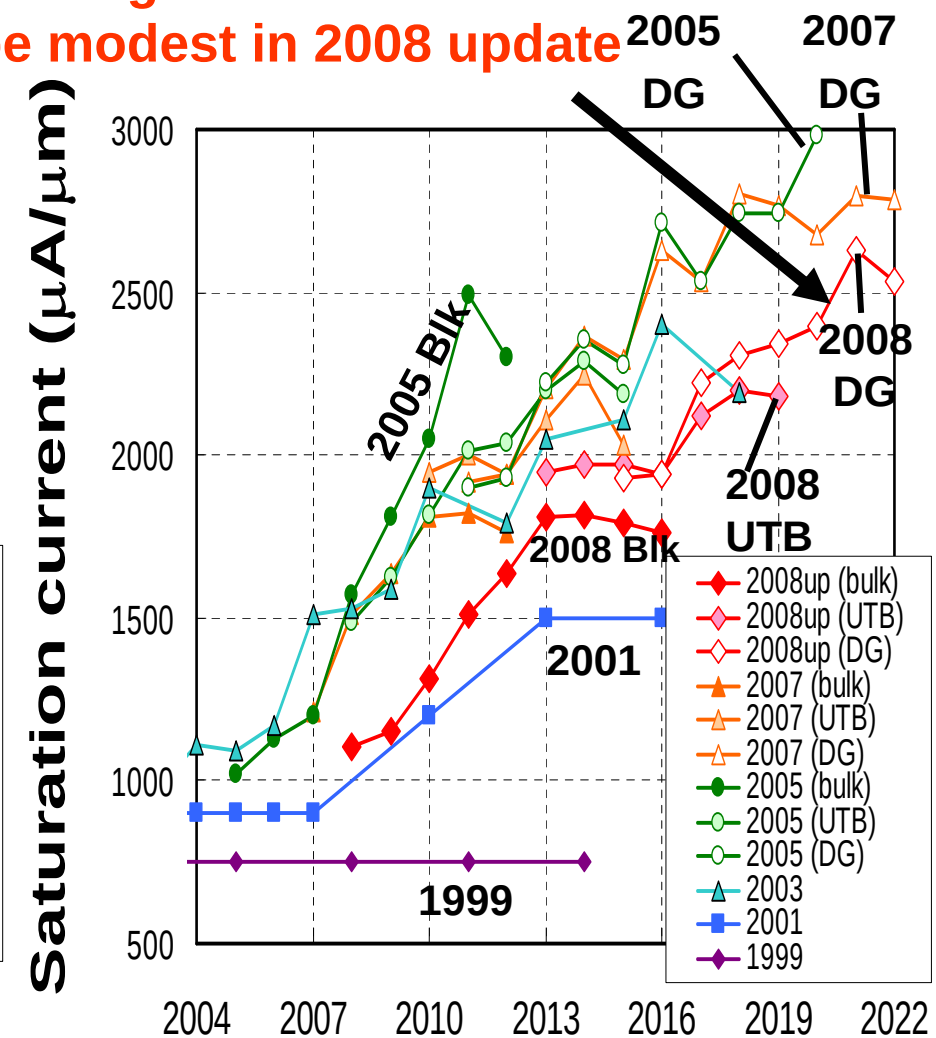
S-D leakage current

Isd-leak has to be stay less than 1μA/μm

Id-sat growth will be modest in 2008 update

Saturated Drain current

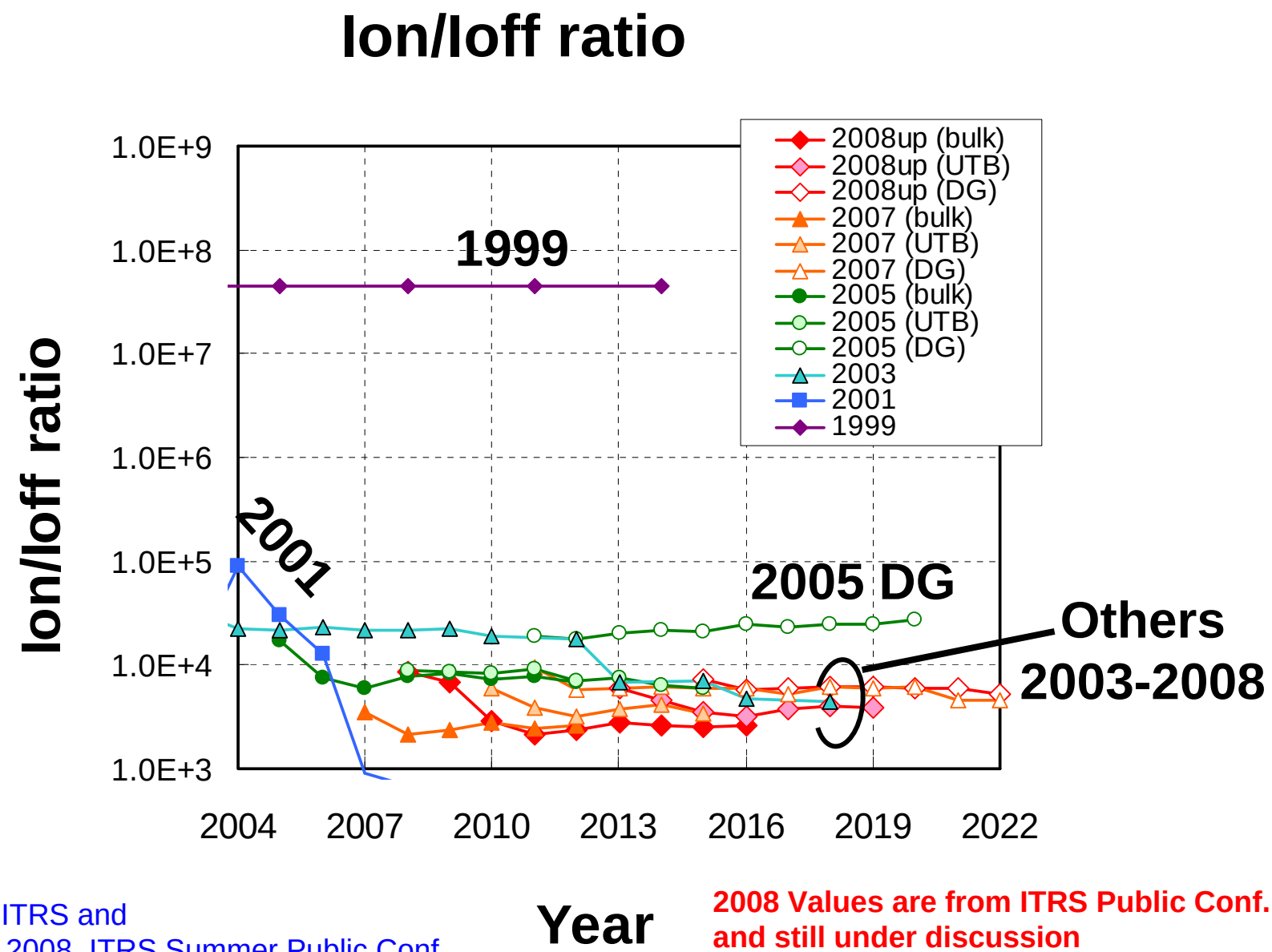




Source: ITRS and 2008 ITRS Summer Public Conf.

2008 Values are from ITRS Public Conf. and still under discussion

ITRS for HP logic



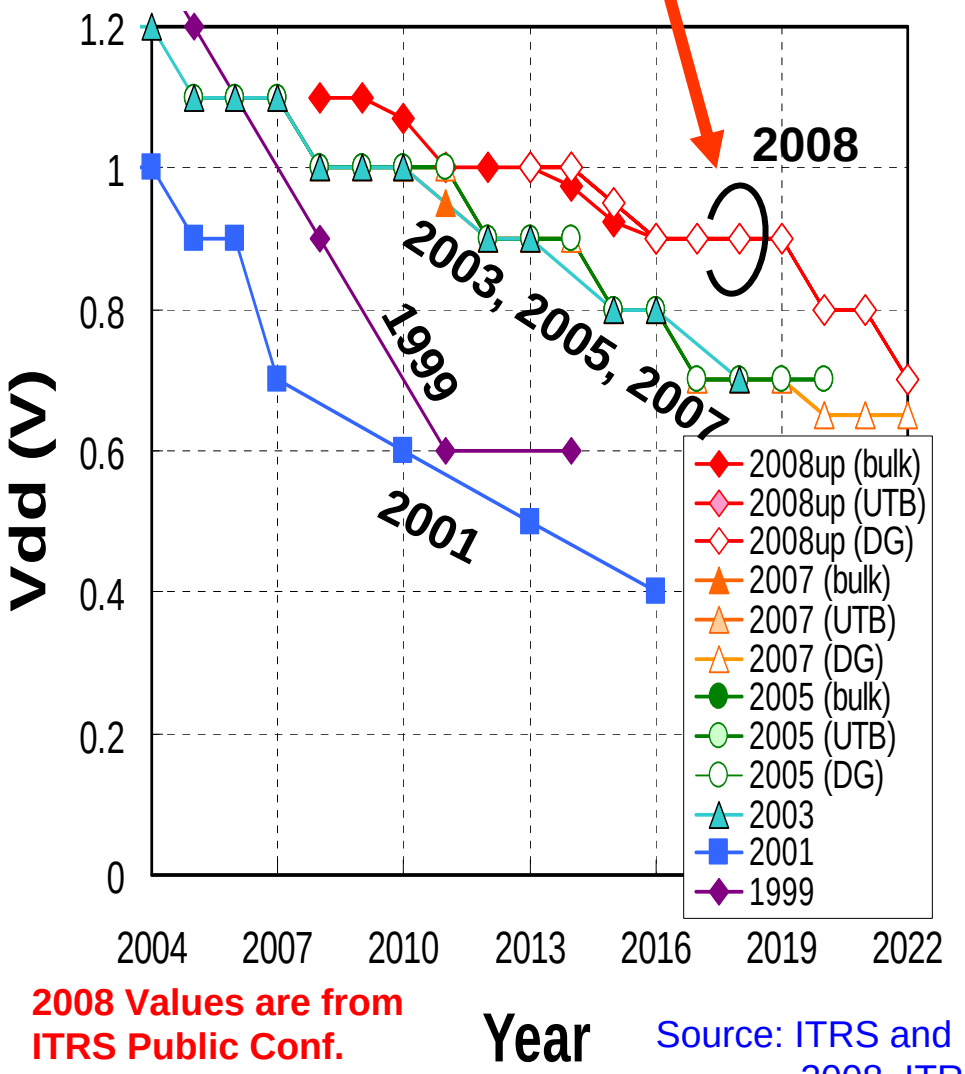
Source: ITRS and
2008 ITRS Summer Public Conf.

2008 Values are from ITRS Public Conf. and still under discussion

ITRS for HP logic

Vdd

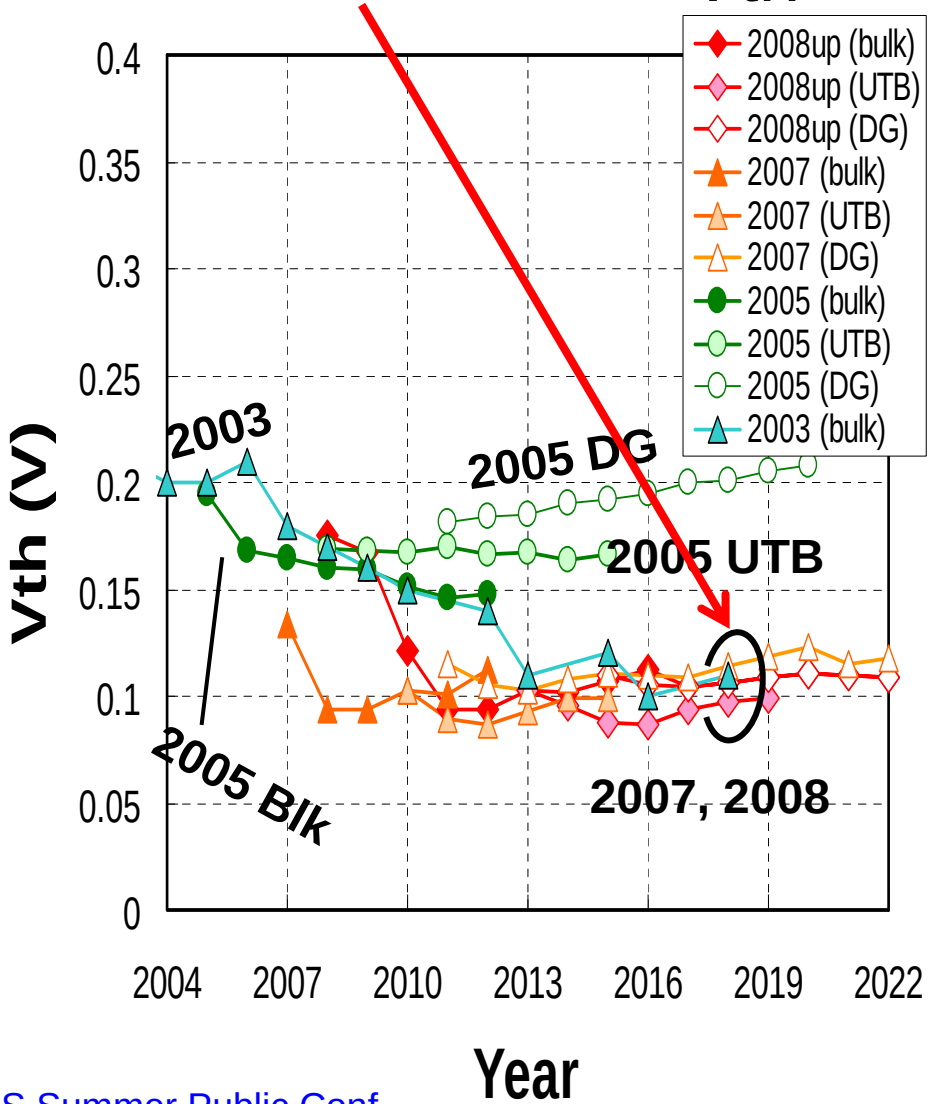
Vdd will stay higher in 2008 update



2008 Values are from ITRS Public Conf. and still under discussion

Saturated Vth

Vth-sat will be around 0.1V

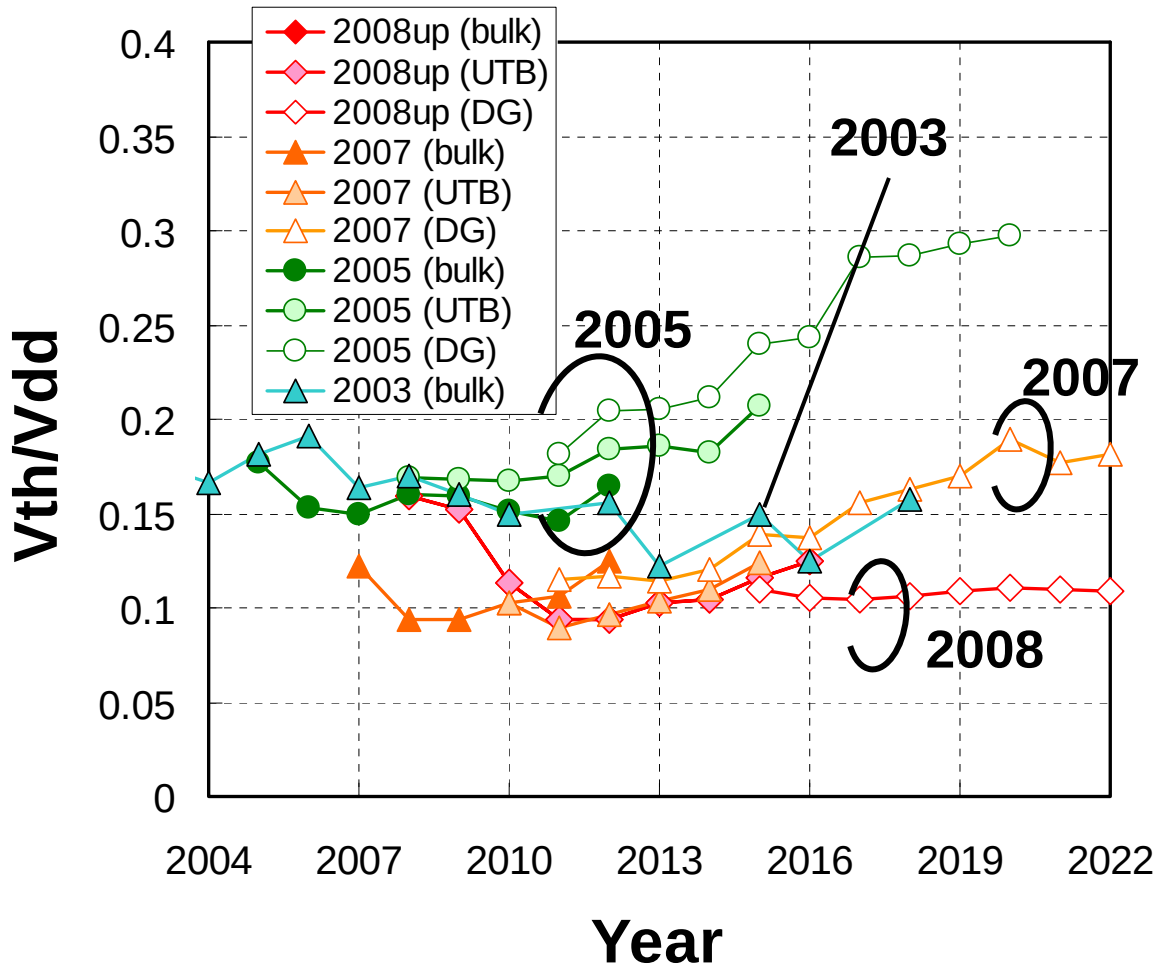


Source: ITRS and 2008 ITRS Summer Public Conf.

ITRS for HP logic

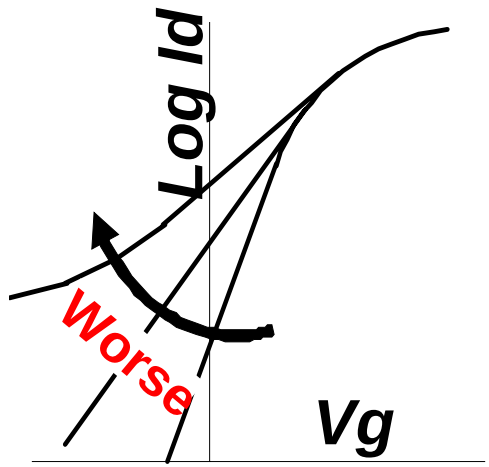
2008 Values are from ITRS Public Conf. and still under discussion

Vth-sat / Vdd



Source: ITRS and
2008 ITRS Summer Public Conf.

SS (Subtheshold Slope) becomes worse in the following cases



1. Improper down-scaling

   Ex. When T_{ox}, W_{dep}, or V_{dd} is not scaled

2. High impurity doping in channel or substrate

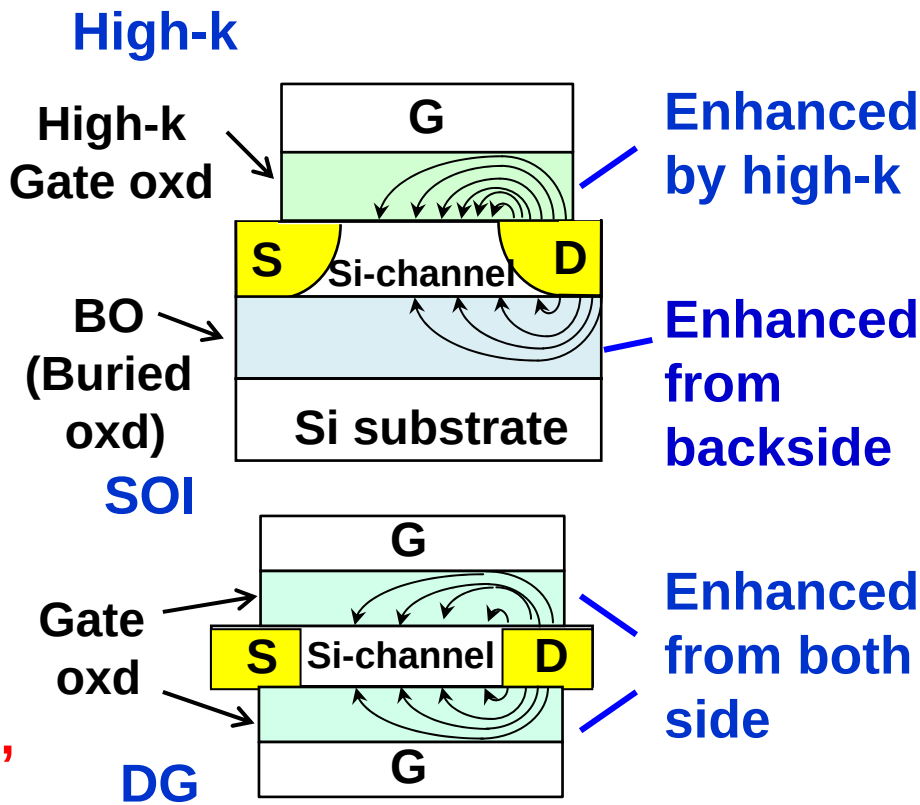
   High impurity Conc.
   → C_D increase
   → SS increase

   $SS = (Ln10)(kT/q)(C_{ox}+C_D+C_{it})/C_{ox}$

3. Enhanced Drain-Electric-field penetration through oxide

   Ex. High-k, SOI,
   Multi-gate (Double gate: DG)

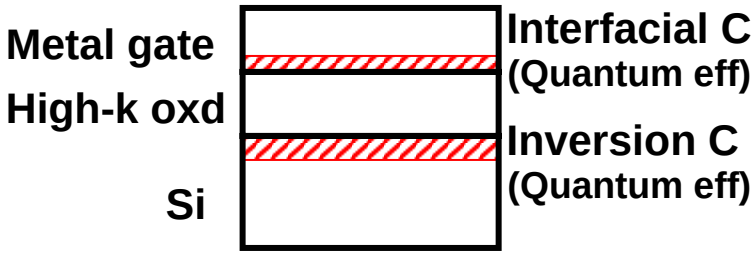
DG and SOI often show better SS, but be careful!

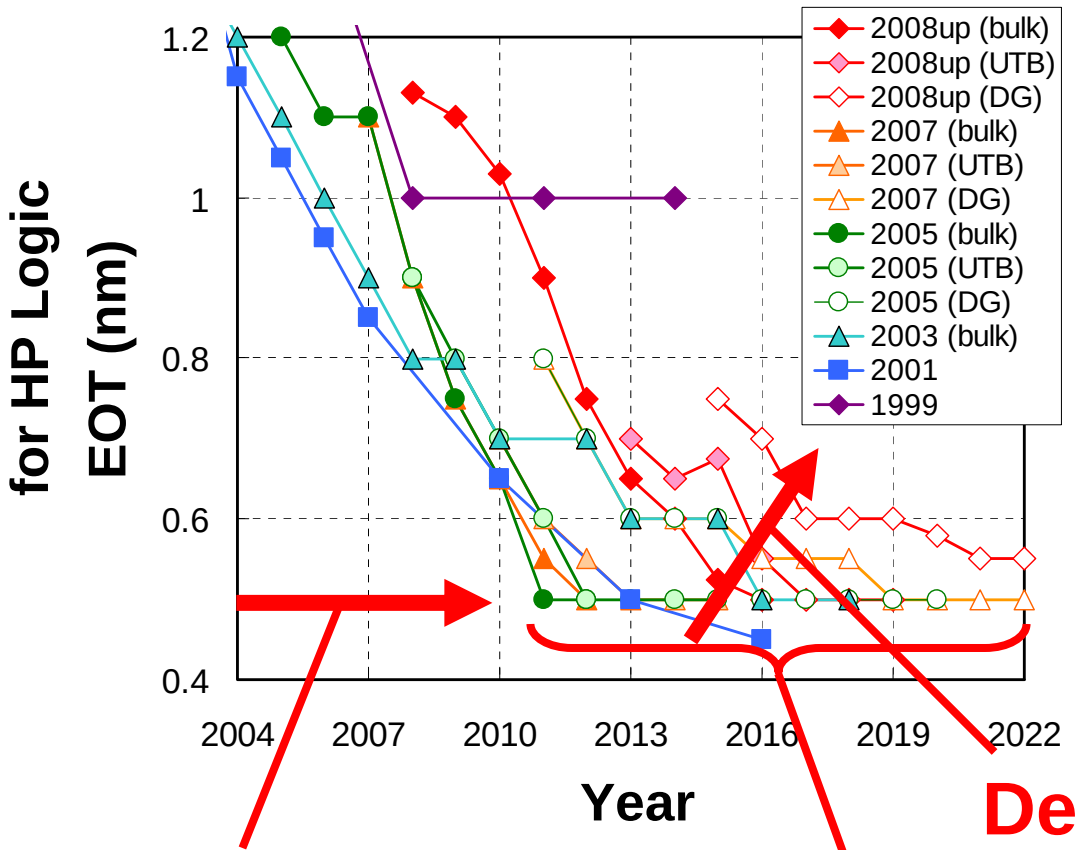


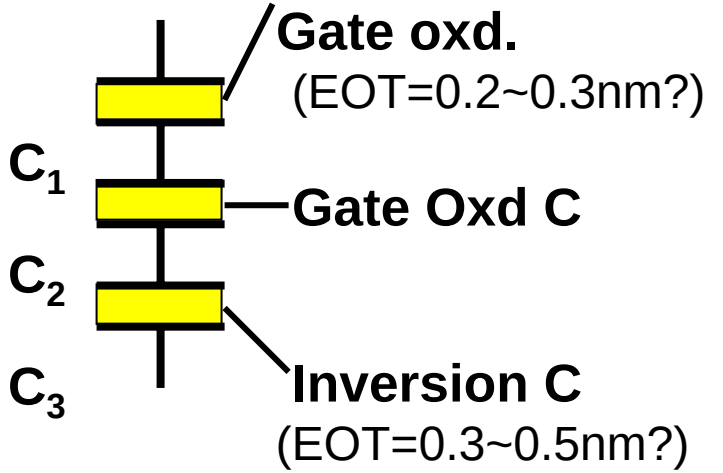
Improper down-scaling

Could we squeeze technologies for ultimate CMOS scaling?

Saturation of EOT thinning is a serious roadblock to proper down-scaling.







$EOT(C_1) + EOT(C_3) > 0.5nm$

Small effect to decrease $EOT(C_2)$ beyond 0.5nm?

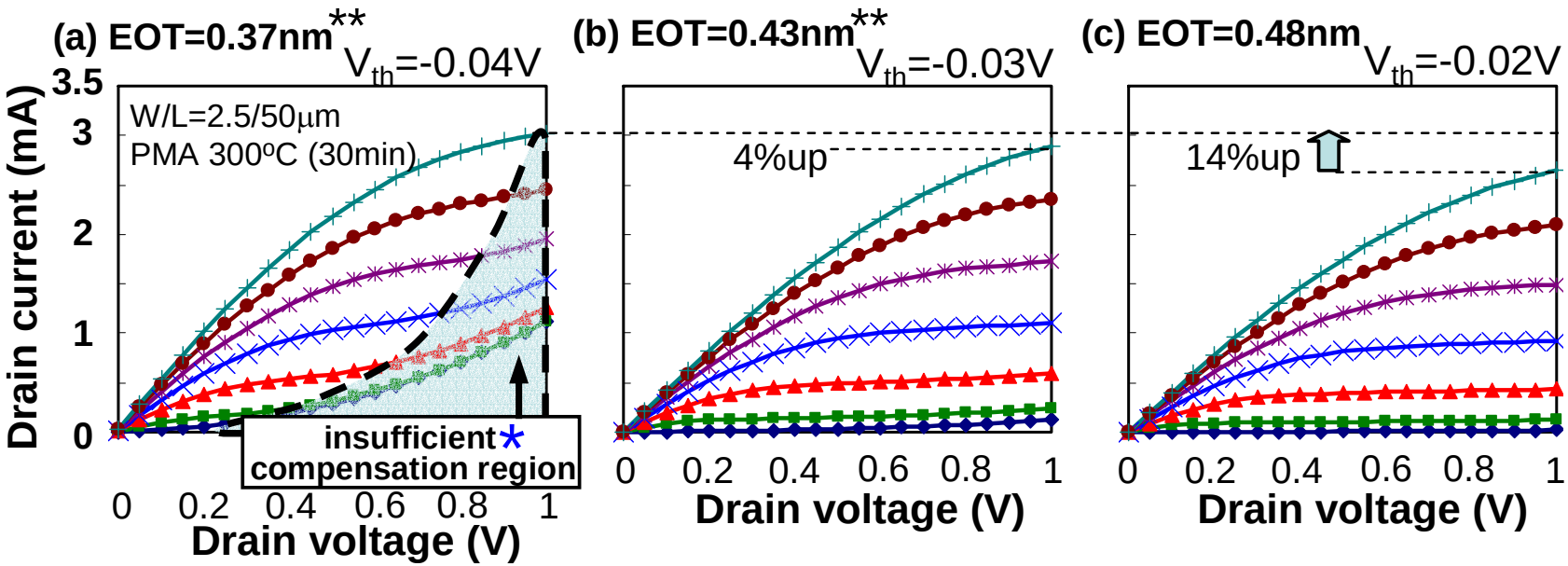
Delay

Is 0.5nm real limit?

Saturation

EOT<0.5nm with Gain in Drive Current is Possible

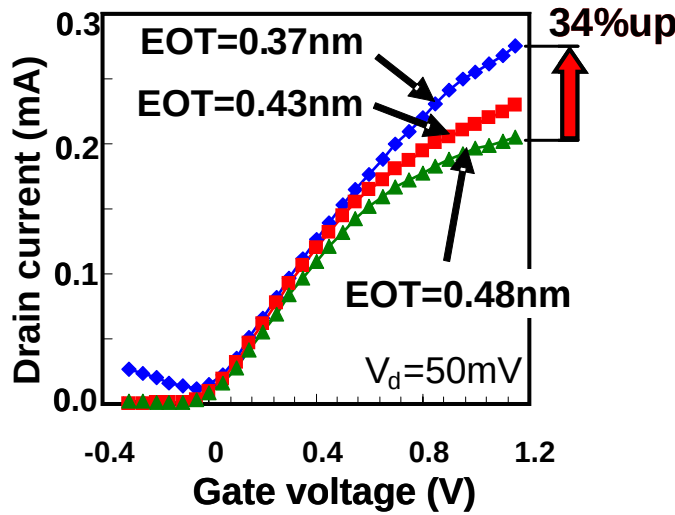
La_2O_3 gate insulator



EOT scaling below 0.5nm

⇩

Still useful for larger drain current



Source: K. Kakushima, K. Okamoto, K. Tachi, P. Ahmet, K. Tsutsui, N.i Sugii, T. Hattori, and H. Iwai, IWDTF 2008, Tokyo, November, 2008

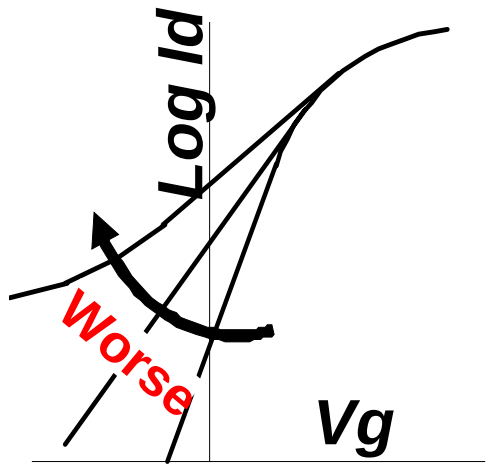
* Because Lg is very large (2.5μm), gate leakage is large in case (a). The gate leakage component was subtracted from measured data for case (a). However, if we make small gate length, the gate leakage current should become sufficiently small to be ignored compared with Id as we verified with SiO_2 gate before (Momose et al.,IEDM 1994). The gate leakage could be suppressed by modifying material and process in future.

** Estimated by Id value

Thus, in future, maybe continuous development of new techniques could make more proper down-scaling possible.

It is difficult to say, but EOT and Vdd may become smaller than expected today.

SS (Subtheshold Slope) becomes worse in the following cases



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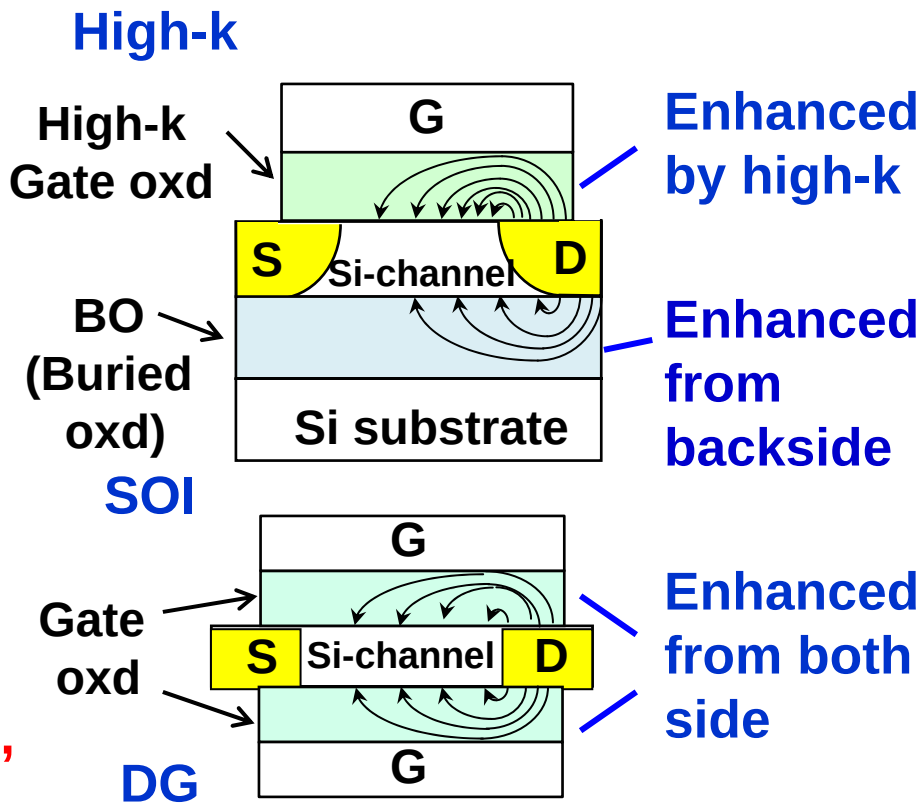
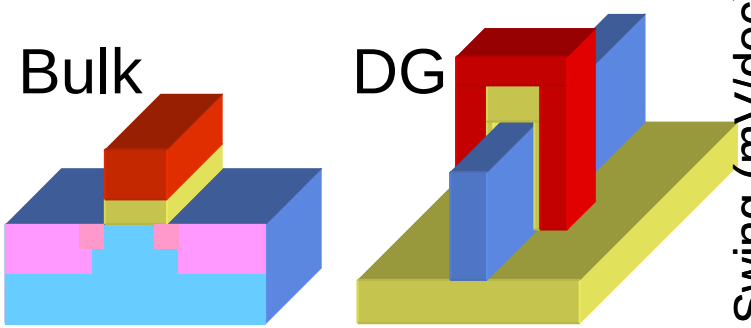


Enhanced D-Electric-field

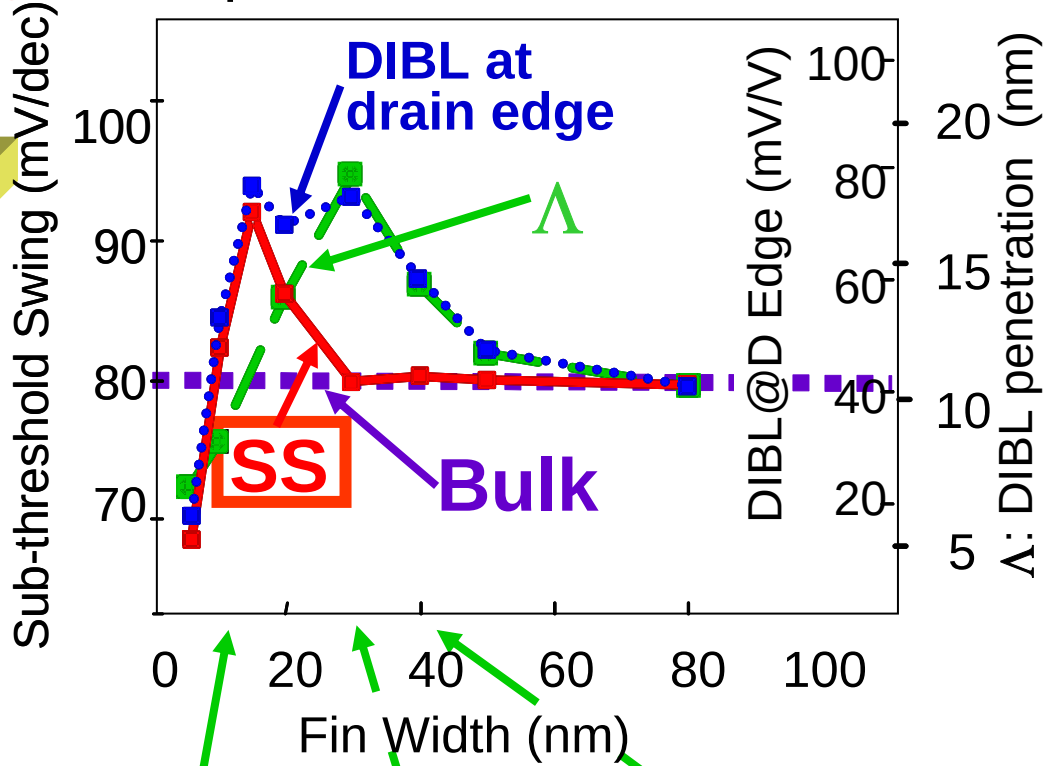


Same parameter condition for both

(2006 ITRS Bulk parameters are used for both Bulk and DG)

Lg=16nm, tox(EOT)=0.5nm,
Dopant@Channel=$8.1X10^{18}cm^{-2}$

Comparison of Bulk and DG



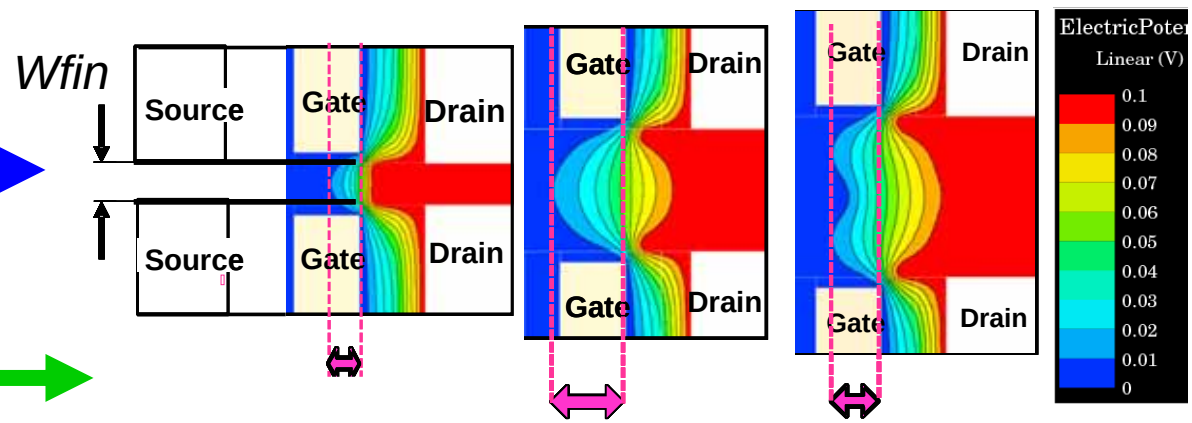
Wfin = 10.7 nm *Wfin* = 30 nm *Wfin* = 40 nm

Source: ECS Fall Meeting, Oct 2008, Honolulu,
Y. Kobayashi, A. B. Sachid, K. Tsutsui, K. Kakushima,
P. Ahmet, V. Ramgopal Rao and H. Iwai.

DIBL: Drain Induced Barrier Lowering

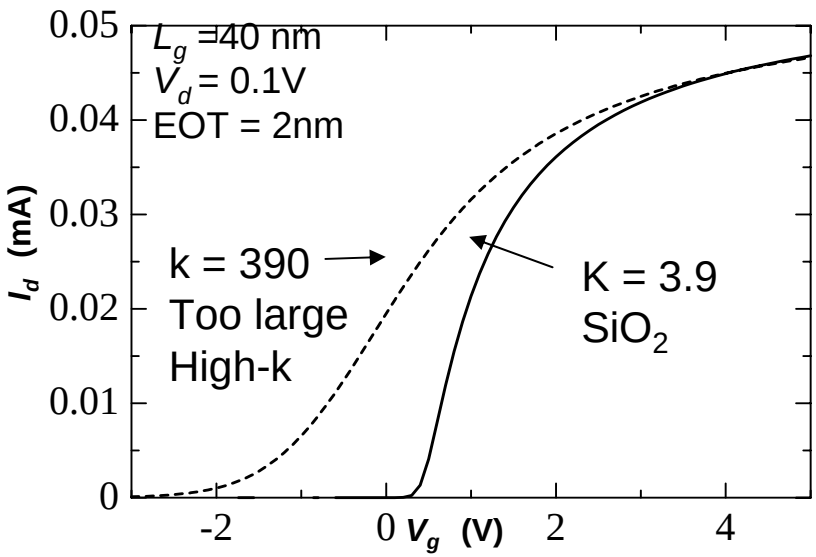
$$\left.\frac{\partial V(x,y)}{\partial Vd}\right|_{Vd=1V}$$

Λ: Penetration Depth of DIBL



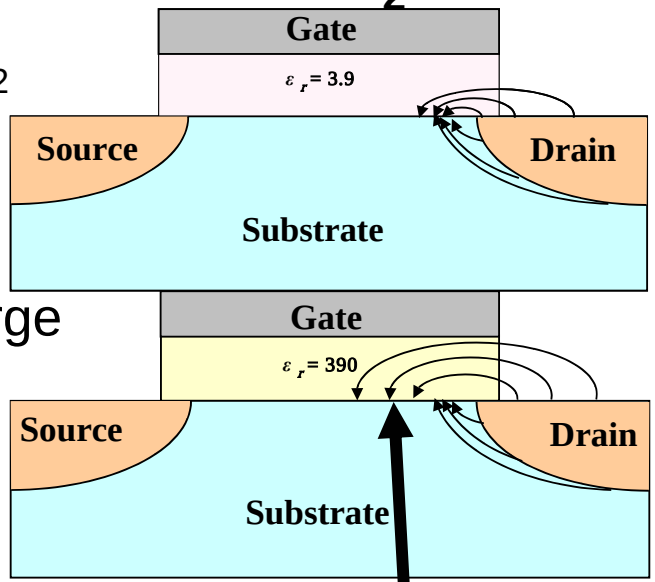
Λ = 7.6nm Λ = 17.1nm Λ = 13.2 nm

Enhanced D-Electric-field



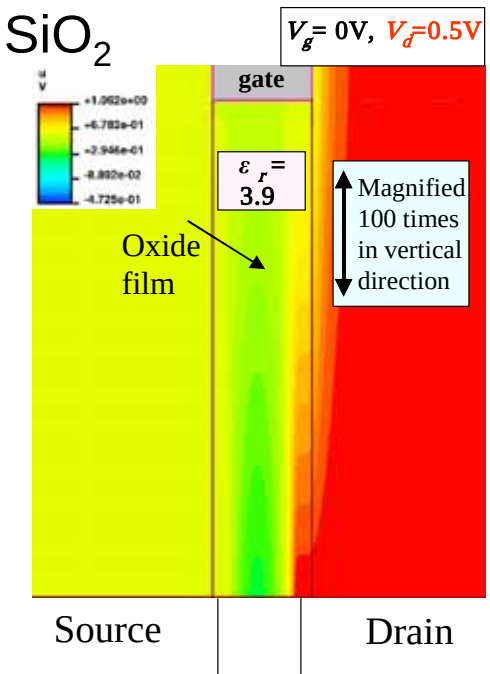
Comparison of High-k and SiO_2 MOSFETs

SiO_2

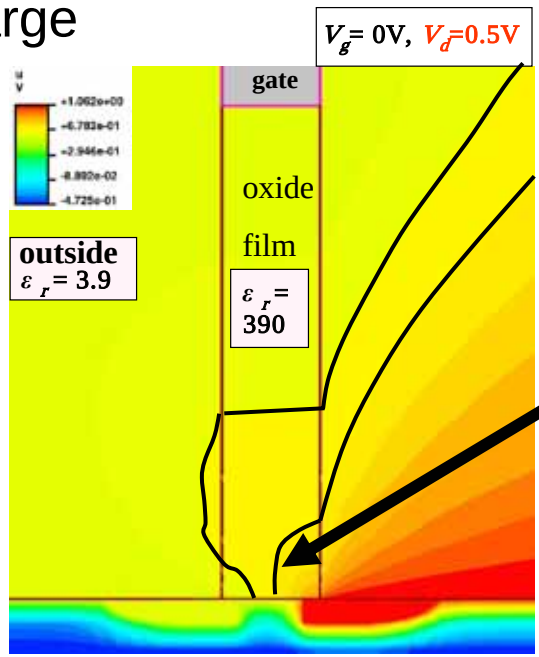


Too large high-k

SiO_2



Too large high-k



Penetration of lateral field from Drain through high-k causes significant short channel effects

R. Fujimura, M. Takeda, K. Sato, S. Ohmi, H. Ishiwara, and H. Iwai, ECS Symp. on ULSI Process Integration II, Volume 2001-2, pp.313-323, 2001,

V_{dd} will stay higher than predicted by previous ITRS roadmaps.

Solution towards Low V_{dd}

Effort to reduce $I_{sd\text{-}leak}$ and increase $I_{d\text{-}sat}$ is important

- Scaling: Proper down-scaling

  -Introduction of Next generation high-k, S/D etc.

  - CD* variation control by lithography and etching techniques

*** CD: Critical dimension**

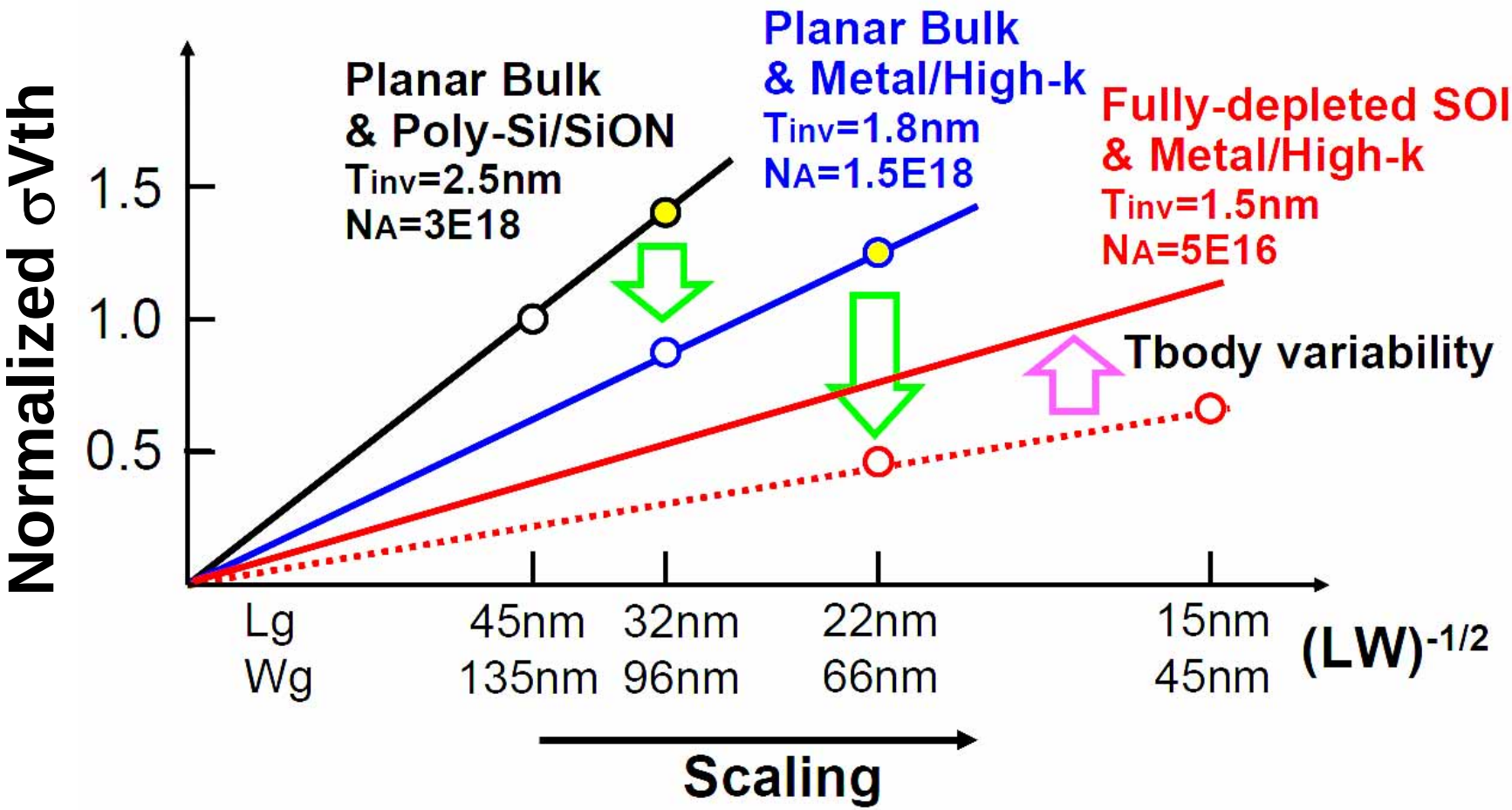
- Structure: Bulk → UTB-SOI → DG → Nanowire

- Variation: Proper scaling by new tech. – High-k, litho. Etc.

  V_{th} adjustment by V_{sub} control

- Circuit techniques: Dynamic and local Multi-V_{dd}, etc.

Random Variability Reduction Scenario in ITRS 2007



Assumption: Random dopant fluctuation is Main source of Random Variability. Line width roughness of Lg and Wg is not considered in this

Source: 2007 ITRS Winter Public Conf.

4. SRAM cell scaling

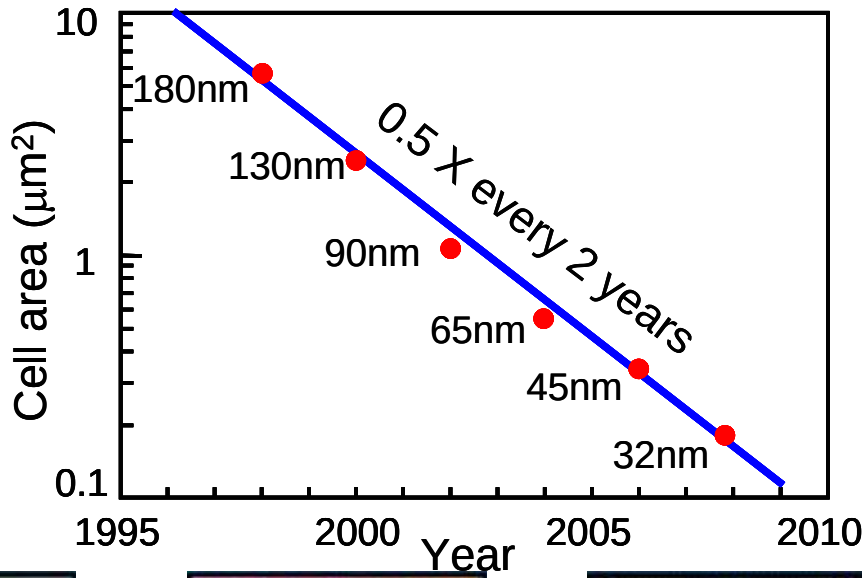
Intel's **SRAM** test chip trend

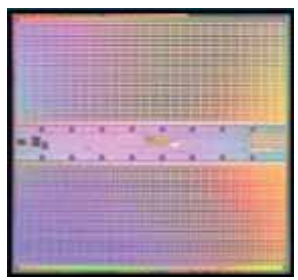
Source: B. Krzanich, S. Natrajan, Intel Developer's Forum 2007
http://download.intel.com/pressroom/kits/events/idffall_2007/BriefingSilicon&TechManufacturing.pdf

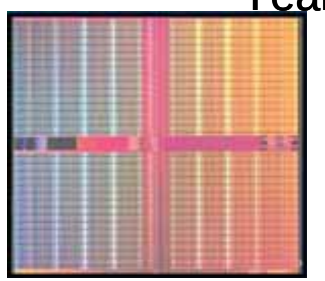
SRAM down-scaling trend has been kept until 32nm and probably so to 22nm

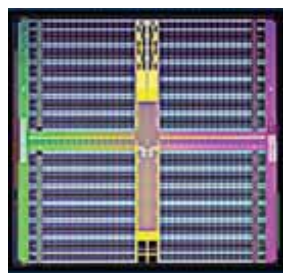
Process name	Lithography	1st production
P1264	65nm	2005
P1266	45nm	2007
P1268	32nm	2009
P1270	22nm	2011

Only schedule has been published









Technology	**90 nm Process**	**65 nm Process**	**45 nm Process**	**32 nm Process**
Cell size	**1.0 μm²cell**	**0.57 μm²cell**	**0.346 μm²cell**	**0.182 μm²cell**
Capacity	50 Mbit	70 Mbit	153 Mbit	291 Mbit
Chip area	109 mm²	110 mm²	119 mm²	118 mm²
Functional Si	February '02	April '04	January '06	September '07

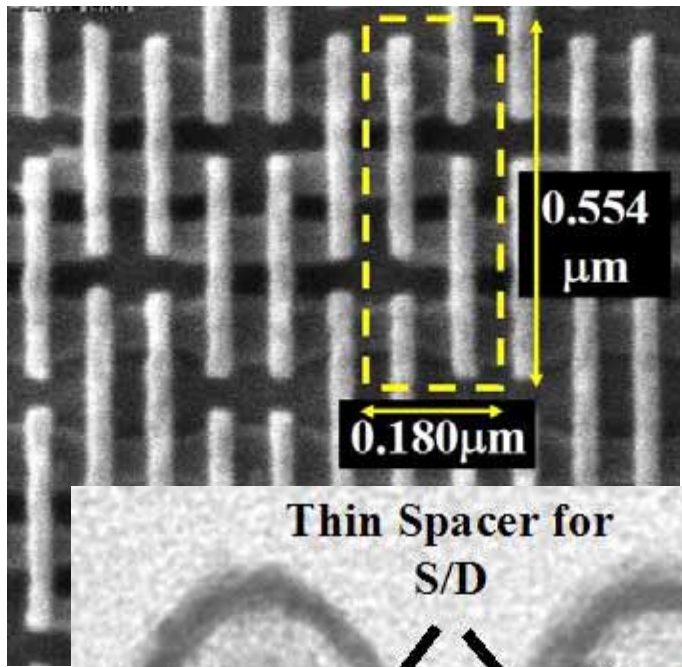
22 nm technology 6T SRAM Cell: Size = 0.1μm

Source: http://www-03.ibm.com/press/us/en/pressrelease/24942.wss

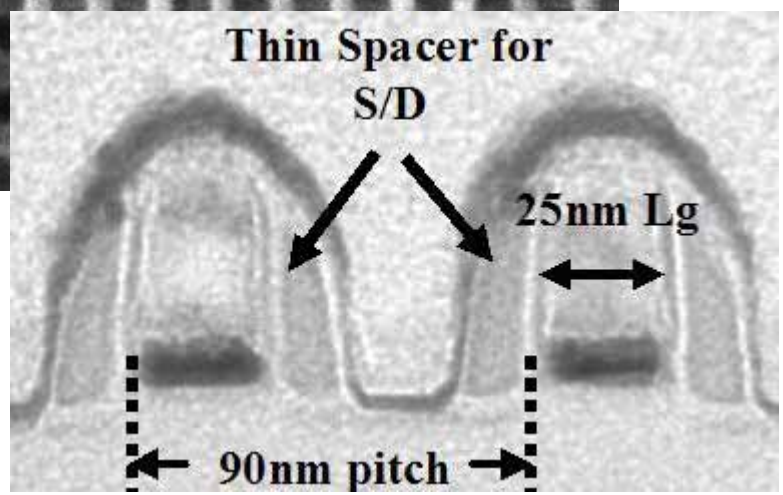
Announced on Aug 18, 2008

Consortium: IBM (NYSE) , AMD, Freescale, STMicroelectronics, Toshiba and the College of Nanoscale Science and Engineering (CNSE)

Static noise margin of 220 mV at 0.9 V



0.1μm cell size is almost on the down-scaling trend



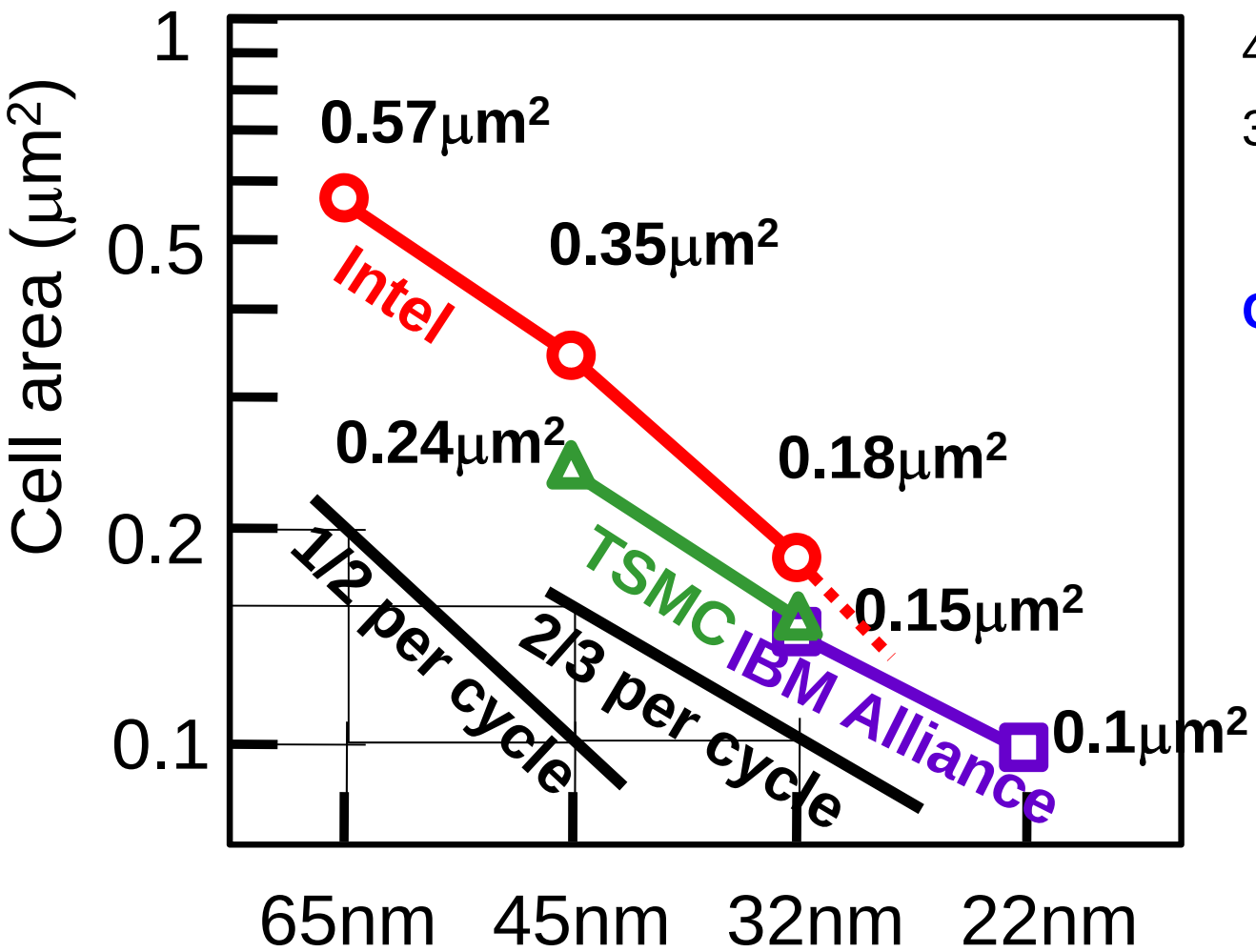
New technologies introduced

- High-NA immersion lithography
- High-K metal gate stacks
- **25 nm gate lengths**
- Thin composite oxide-nitride spacers
- Advanced activation techniques
- Extremely thin silicide
- Damascene copper contacts

Source: IEDM2008 Pre-conference Publicity http://www.btbmarketing.com/iedm/

Cell size reduction trends

1/2 or 2/3 per cycle?



Intel

Functional Si

65nm Apr.2004

45nm Jan.2006

32nm Sep.2007

TSMC

Conference (IEDM)

45nm Dec.2007

32nm Dec.2007

IBM Alliance (Consortium)

Conference (IEDM)

32nm Dec.2007

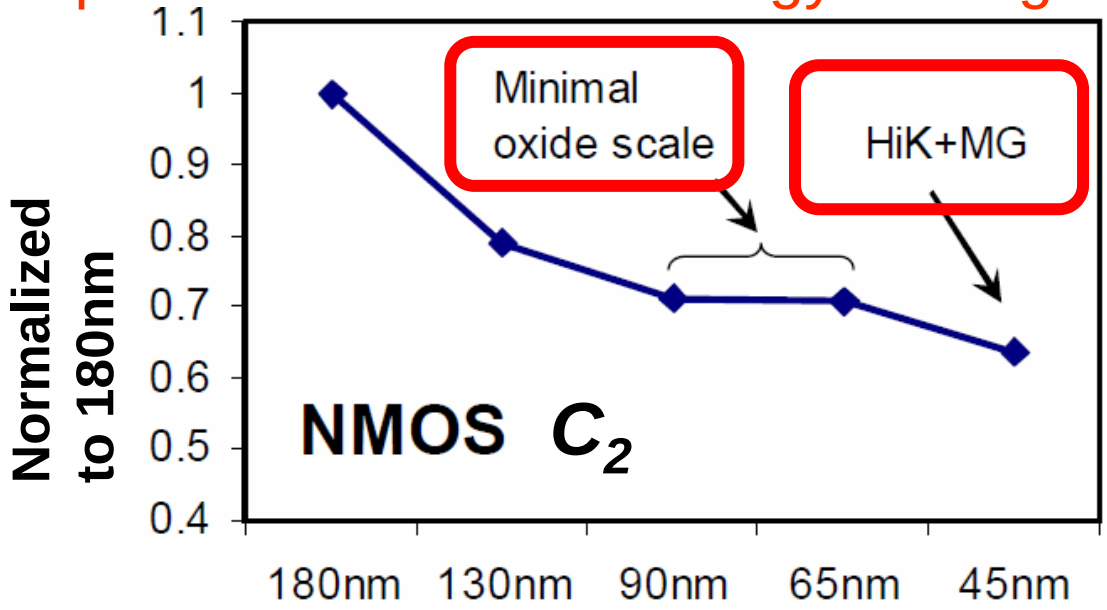
Press release

22nm Aug.2008

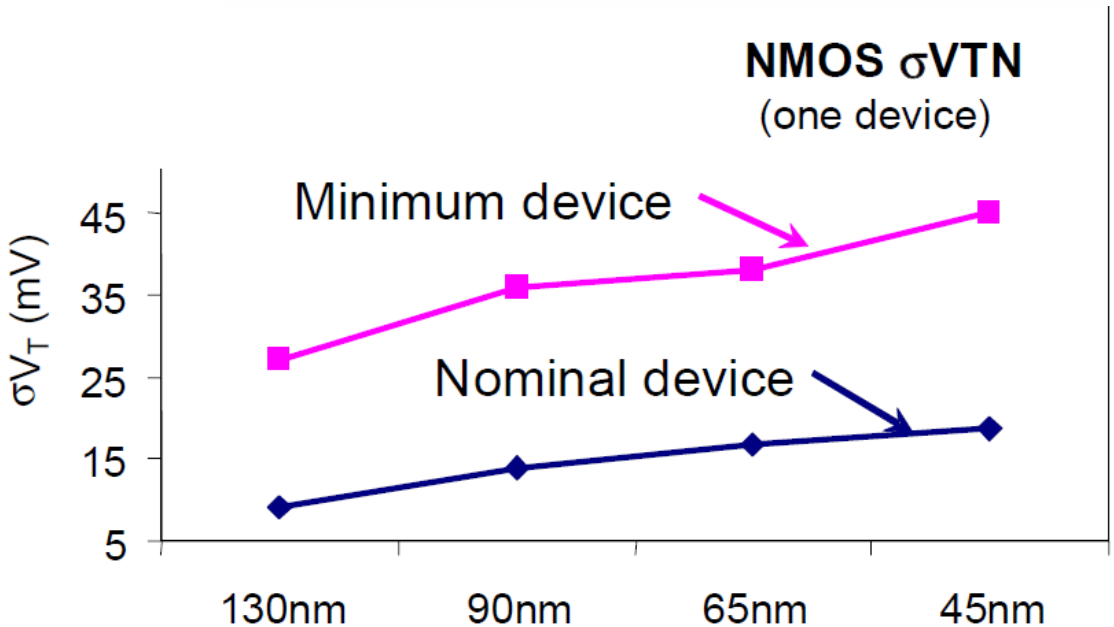
NMOS Mismatch Coefficient (C_2) improvement with technology scaling

$$\sigma V_{Tran} = \left(\frac{\sqrt[4]{4q^3\varepsilon_{si}\phi_B}}{2}\right)\cdot\frac{T_{ox}}{\varepsilon_{ox}}\cdot\left(\frac{\sqrt[4]{N}}{\sqrt{Weff\cdot Leff}}\right)$$

$$= \frac{1}{\sqrt{2}}\left(\frac{c_2}{\sqrt{Weff\cdot Leff}}\right)$$



σV_{Tran}

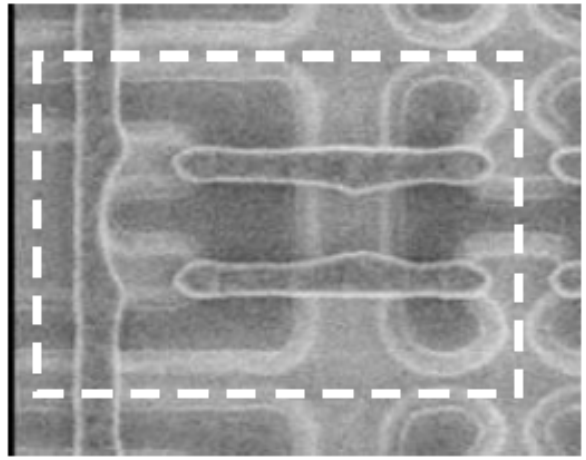


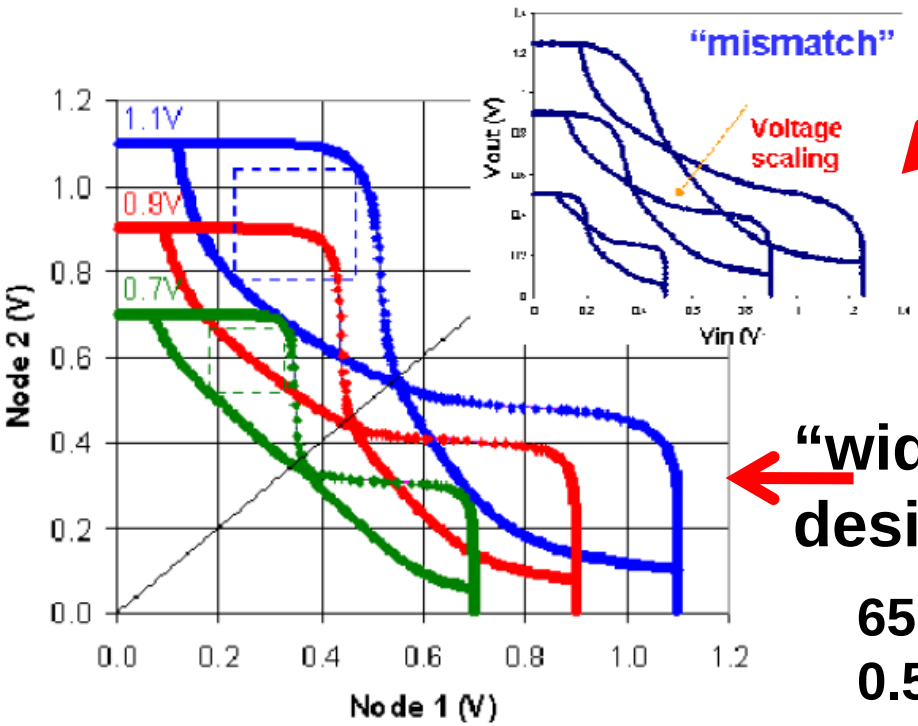
Source: K.J.Kuhn
IEDM 2007

Mismatch improvement by layout (Intel)

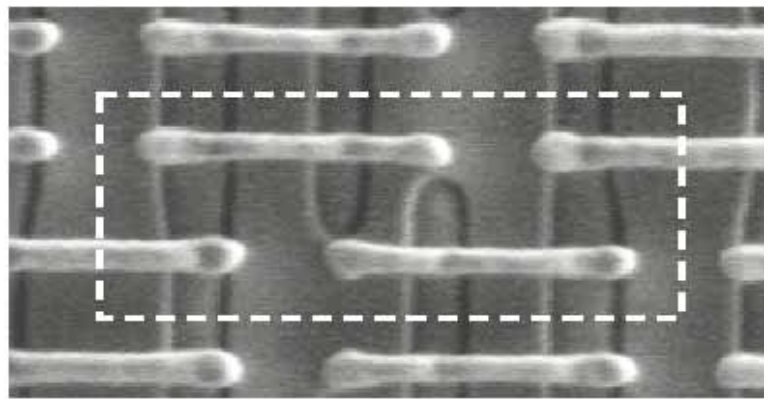
“tall” design

90nm :1.0 μm²





“wide” design

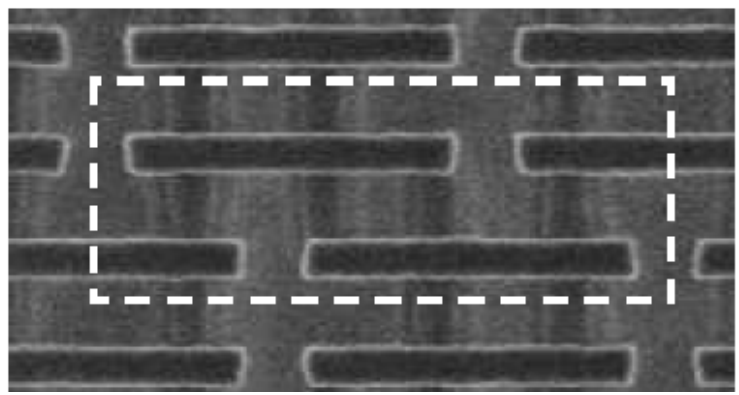


65nm : 0.57 μm²

Source: K. J. Kuhn
IEDM2007 Tech. Dig. pp.471

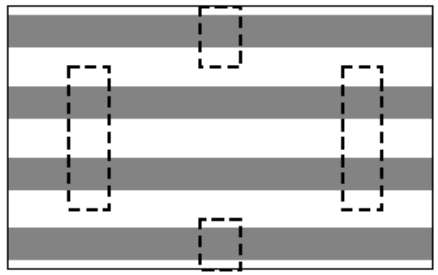
“wide” design (Square endcaps)

45nm 0.346 μm²

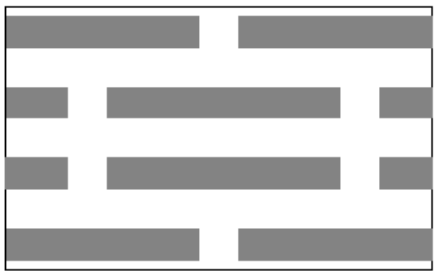


Double patterning for square endcap

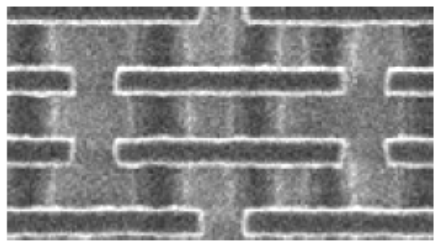
a) Pattern gate lines/spaces



b) Pattern cut mask



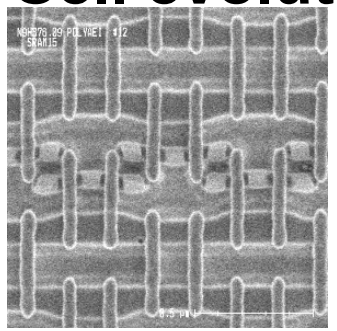
c) Final gate pattern



d) Intel 45nm SRAM cell

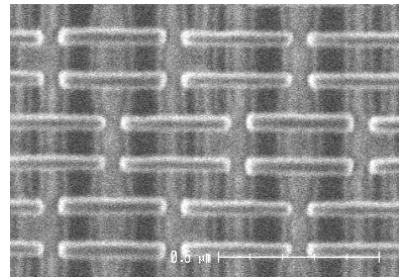
Source: M. Bohr, ICSICT2008

Cell evolution is similar



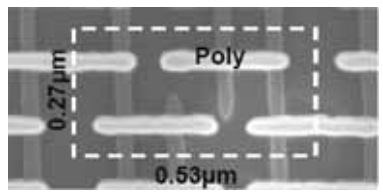
TSMC 45nm

IEDM 2007



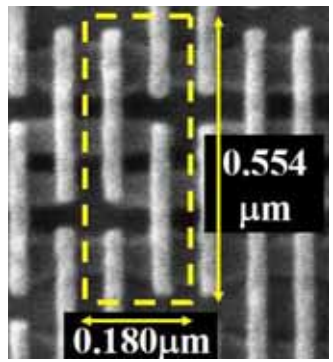
TSMC 32nm

IEDM 2007



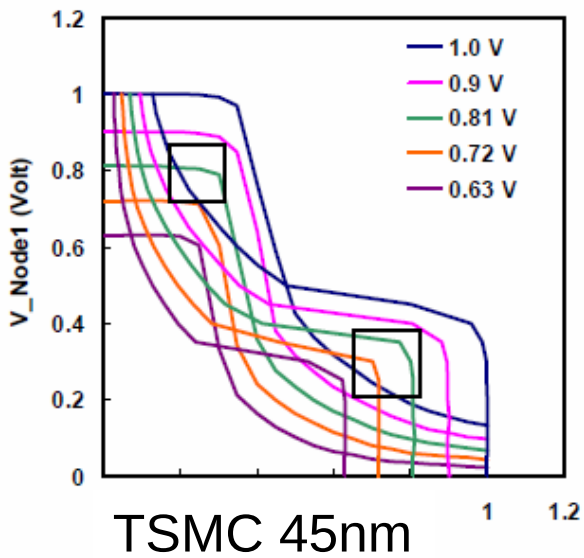
IBM Alliance 32nm

IEDM 2004

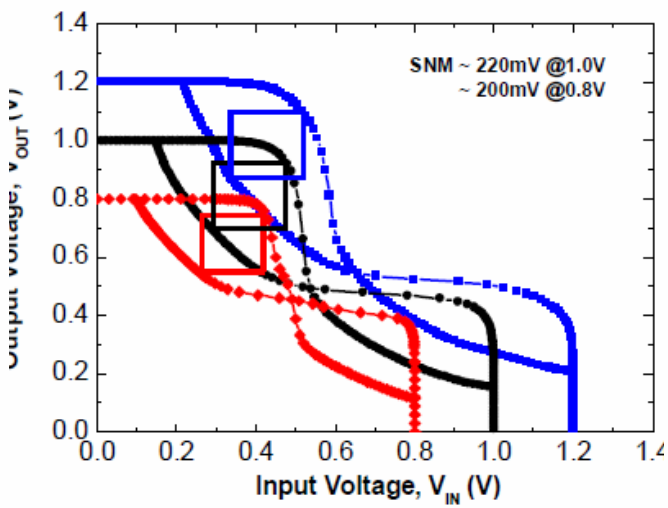


IBM Alliance 22nm

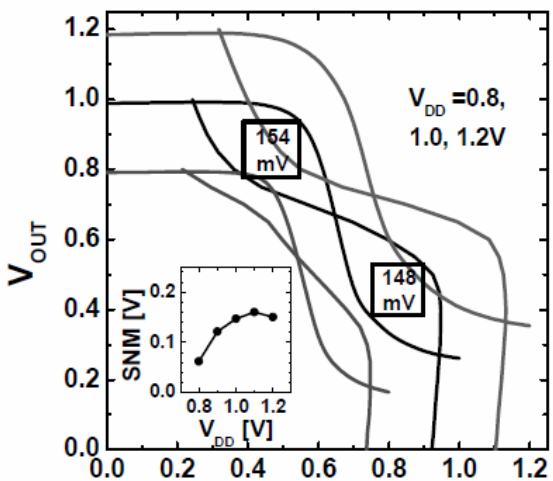
IEDM 2008



TSMC 45nm



TSMC 32nm



IBM Gr. 32nm

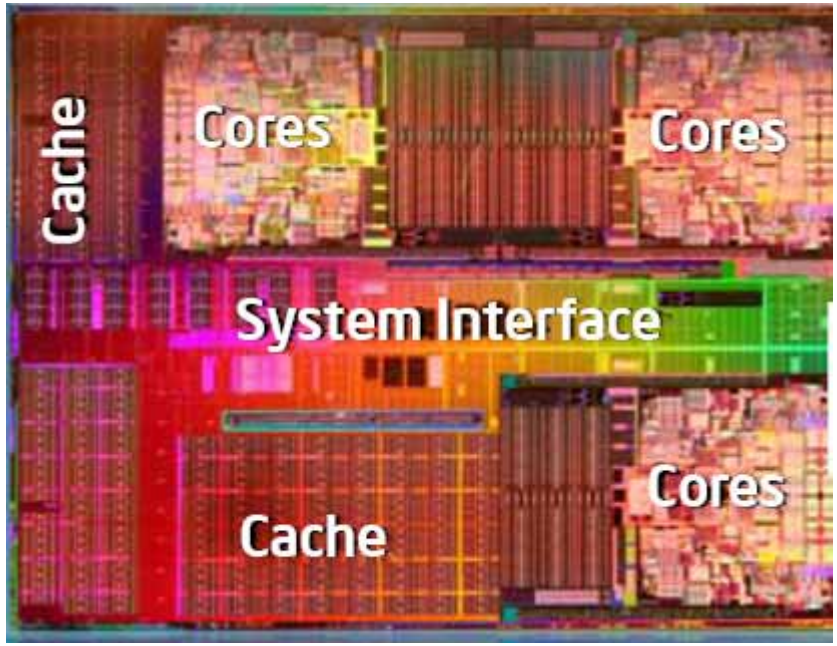
Most Difficult part of SRAM down-scaling is Vdd down-scaling

Density of on-chip cache SRAM memory is high and thus, Vth cannot be down-scaled too much because of large Isd-leak

Also, under low Vdd, read- and write margin degrades, data retention degrade.

Thus, Vdd down-scaling is more severe in SRAM than logic part of the circuits

Intel® Xeon® 7400 Series (Dunnington)



45 nm high-k6 cores

16MB shared L3 cache

Source: Intel Developer Forum 2008

Cache occupies huge area

→ Cell size of SRAM should be minimized

→ Isd-leak should be minimized

→ Vth are often designed to be higher than Min. logic Vth

→ Lg are often designed to be larger than Min. logic Lg

Future Directions For Improving Vmin

- Application
  - Improvement in voltage and temperature tolerance
- Package
  - Separated array / logic voltage to minimize logic noise effect on SRAM
- Design
  - Higher array VDD and improved on-chip supply robustness
  - Increased redundancy
  - Improved timings
  - Cells per BL hierarchical BL structure
  - Write/Read assist and sense-amp design
- Cell and Process
  - Improved bit cell optimization
- NFET/PFET centering and Beta/Gamma control
- Minimize device fluctuation by limiting device-geometry scaling

larger cell

- Lpoly, Weff, LER
  - Leakage / defect mechanisms

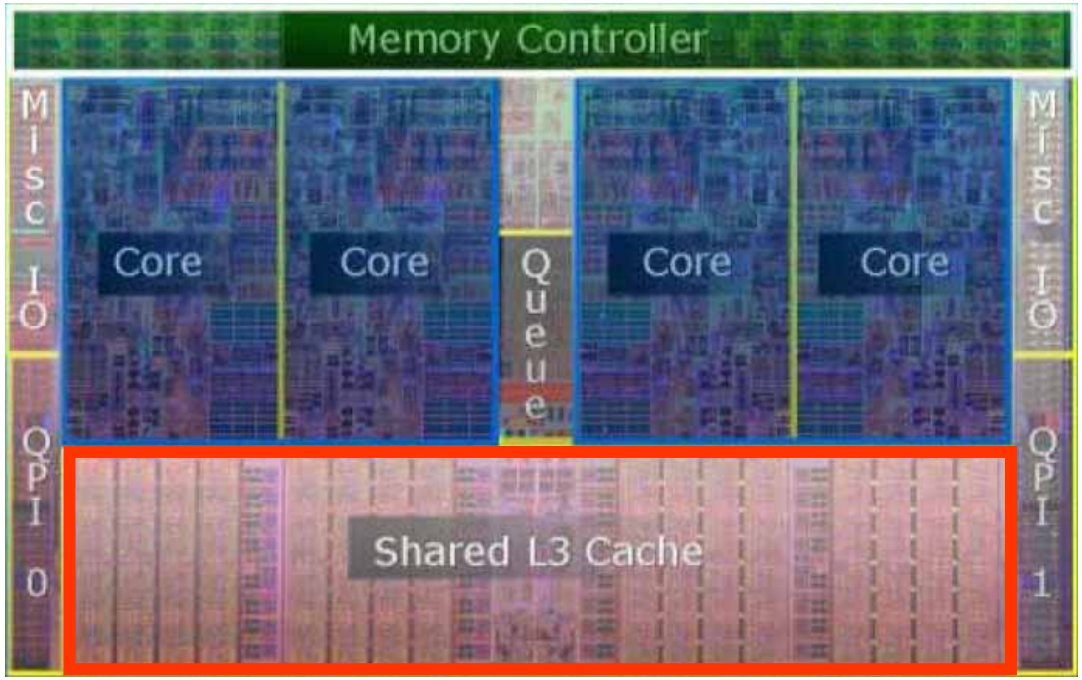
Source: Harold Pilo IEDM2006 Short Course

Nehalem(Intel) 2,4 or 8 Cores

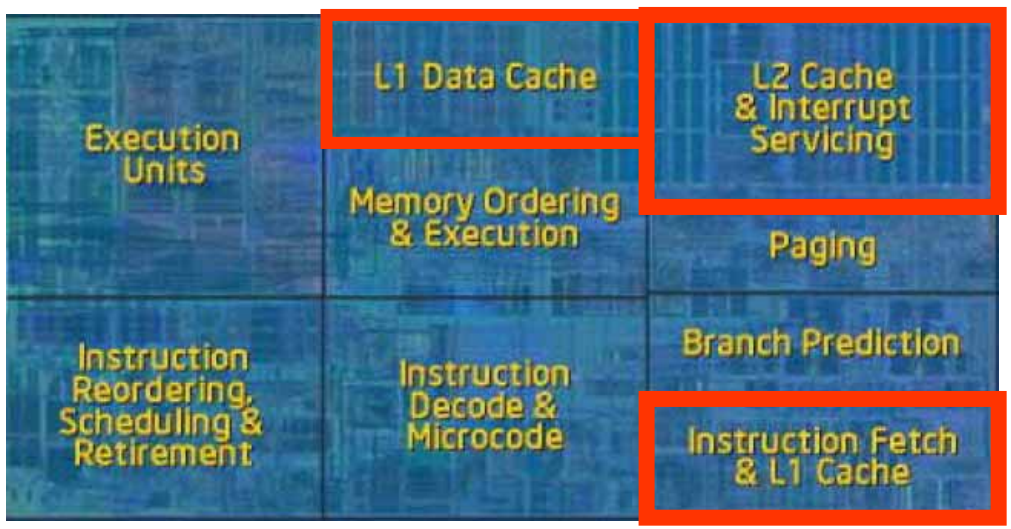
Voltage/Frequency Partitioning

- DDR Vcc
- Core Vcc
- Uncore Vcc

Dynamic Power Management



Chip



Core

8T SRAMCell

32kB L1 I -cache

32kB L1 D-cache

256kB L2 -cache

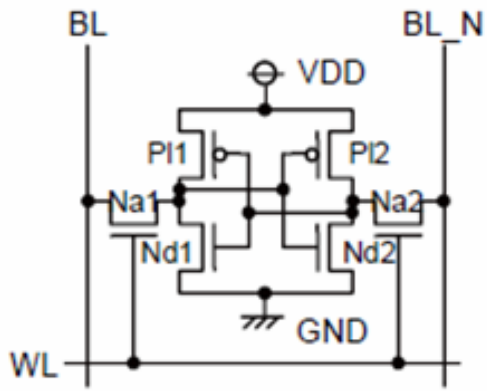
6T SRAMCell

8 MB L3 cache

Source: Intel Developer Forum 2008

6T and 8T Cell

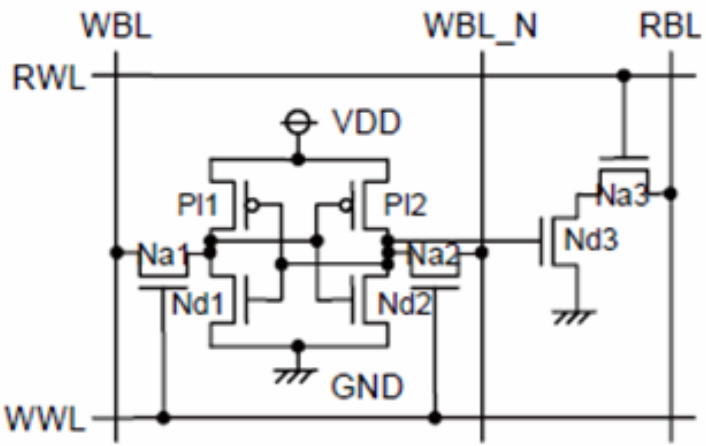
6T Cell



Cell size is small

For high density use

8T Cell



Add separate read function

Cell size increase 30%

For low voltage use

Source: Morita et. al, Symp. on VLSI Circ. 2007

5. Roadmap for further future as a Personal View

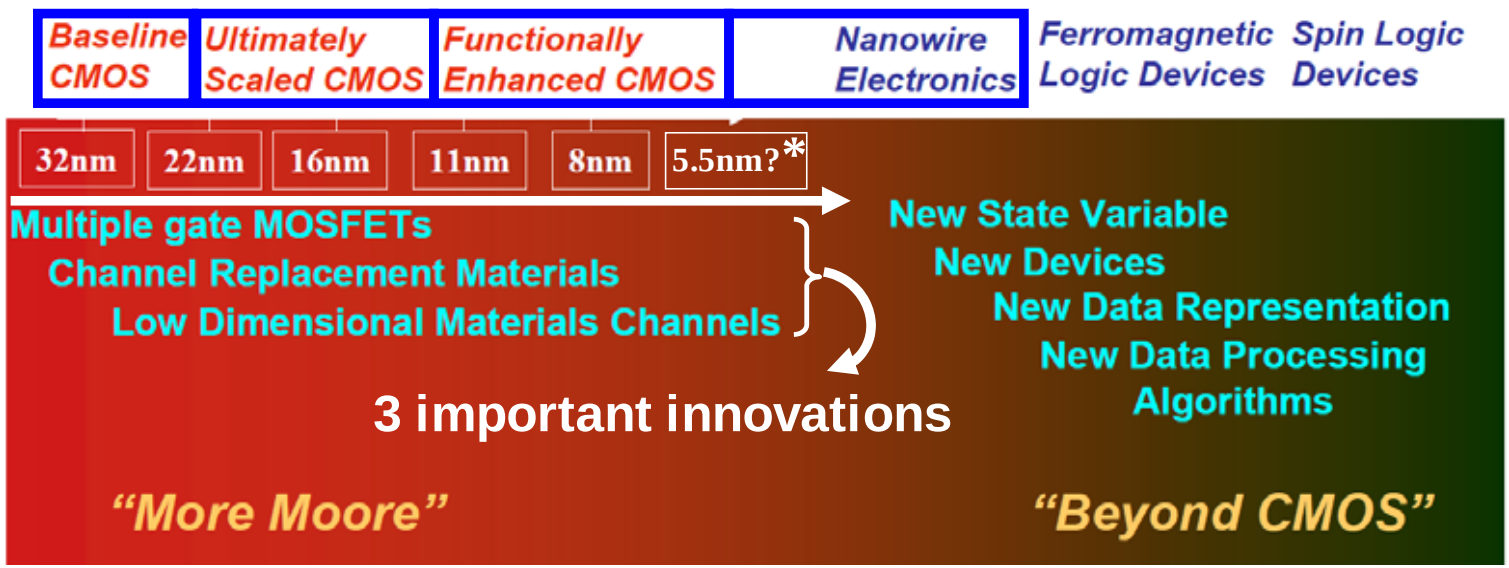
-There will be still 4~6 cycles (or technology generations) left until we reach 11 ~ 5.5 nm technologies, at which we will reach down-scaling limit, in some year between 2020-30 (H. Iwai, IWJT2008).

-Even After reaching the down-scaling limit, we could still continue R & D, seeking sufficiently higher Id-sat under low Vdd.

-Two candidates have emerged for R & D

1. Nanowire/tube MOSFETs
2. Alternative channel MOSFETs (III-V, Ge)

- Other Beyond CMOS devices are still in the cloud.



ITRS figure edited by Iwai

Source: 2008 ITRS Summer Public Conf.

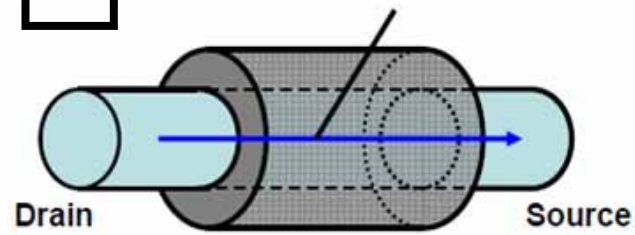
***5.5nm? was added by Iwai**

Si nanowire FET with Semi-1D Ballistic Transport

Merit of Si-nanowire

0

Reduction in Ioff (Isd-leak)



Good control of Isd-leak by surrounding gate

Source: Y. Lee., T. Nagata., K. Kakushima., K. Shiraishi, and H. Iwai, IWDTF 2008, Tokyo, November, 2008

Trade off

Carrier scattering probability

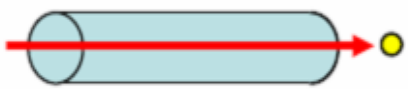
Small **Large**

# of quantum channel

Small **Large**

Increase in Ion (Id-sat)

1



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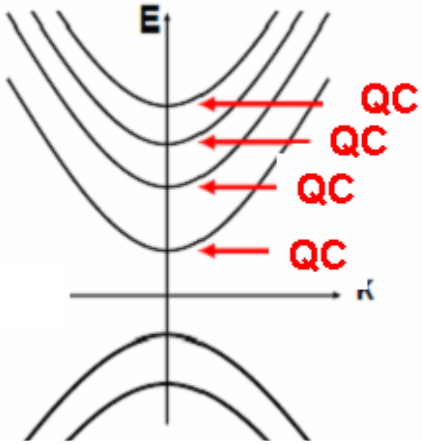
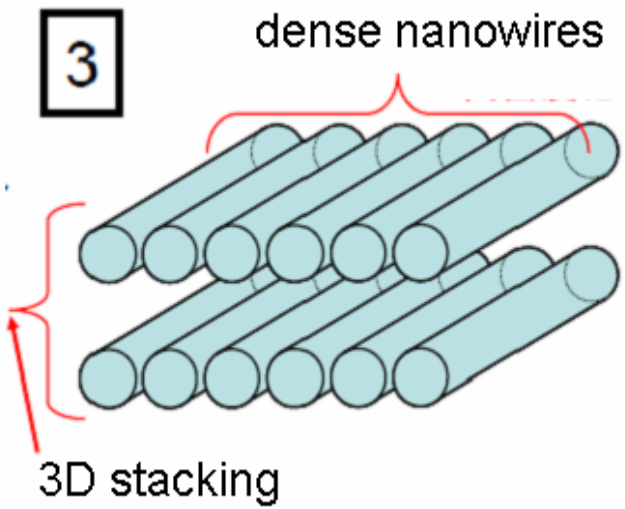


High Conduction (1D)

Go=77.8μS/wire

3



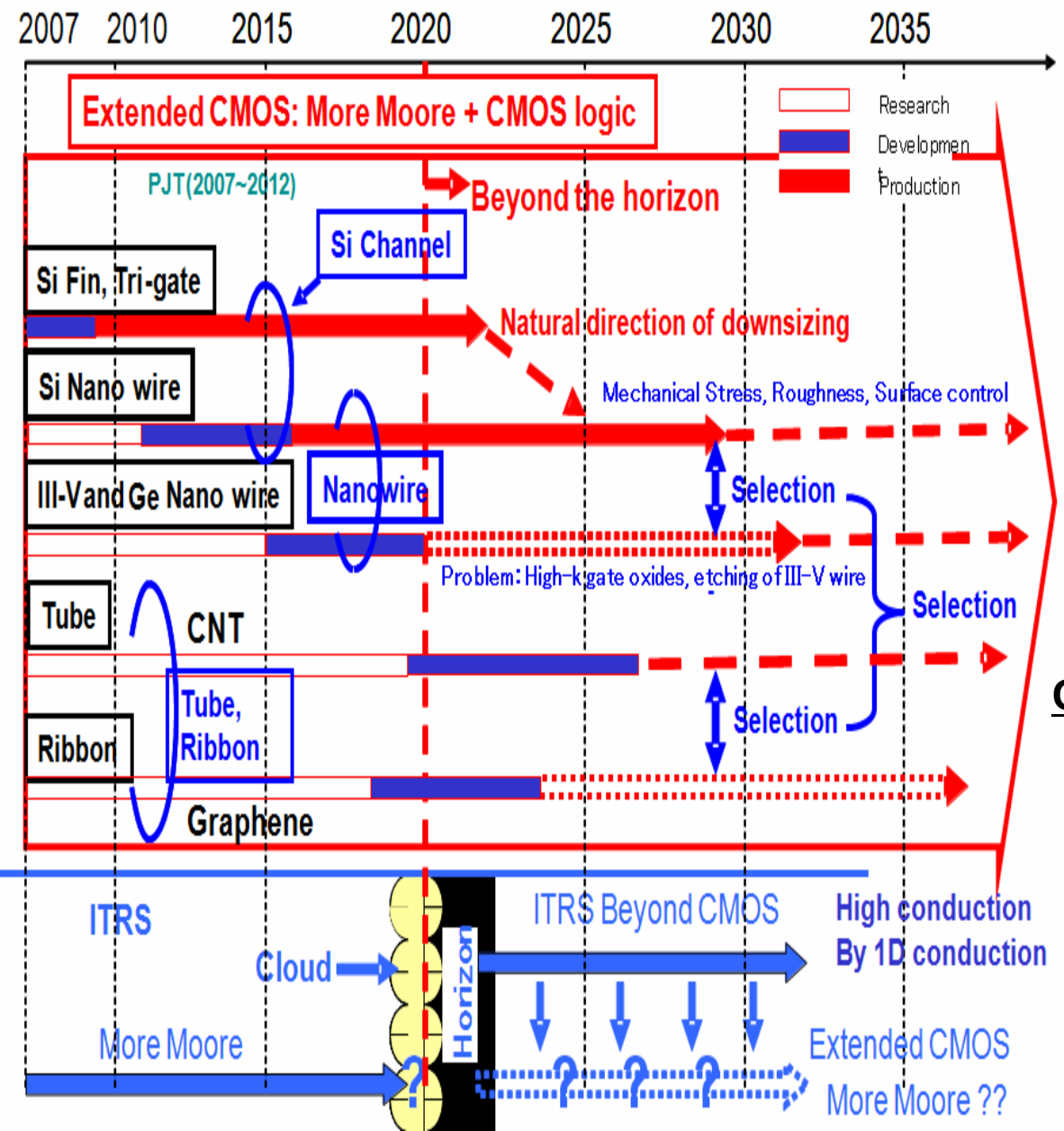
Multiple quantum channel (QC) used for conduction

High-density lateral and vertical integration

Source: T. Ohno, K. Shiraishi, and T. Ogawa, Phys. Rev. Lett. ,1992

Our roadmap for R &D

Source: H. Iwai, IWJT 2008



Current Issues

Si Nanowire

Control of wire surface property

Source Drain contact

Optimization of wire diameter

Compact I-V model

III-V & Ge Nanowire

High-k gate insulator

Wire formation technique

CNT:

Growth and integration of CNT

Width and Chirality control

Chirality determines conduction types: metal or semiconductor

Graphene:

Graphene formation technique

Suppression of off-current

Very small bandgap or no bandgap (semi-metal)

Control of ribbon edge structure which affects bandgap

Long term roadmap for development

Source: H. Iwai, IPFA 2006

We do know system and algorithms are important!

But do not know how it can be by us for use of bio?

Size (Gate length etc)

5 nm?

New Materials, New Process, New Structure (Logic, Memory)

Hybrid integration of different functional Chip
Increase of SOC functionality

3D integration of memory cell
3D integration of logic devices

Miniaturization of Interconnect son P C B
(Printed Circuit Board)

Low cost for LSI process
Revolution for C R, Equipment, Wafer

Introduction of algorithm
of bio-system
Brain of insects, human

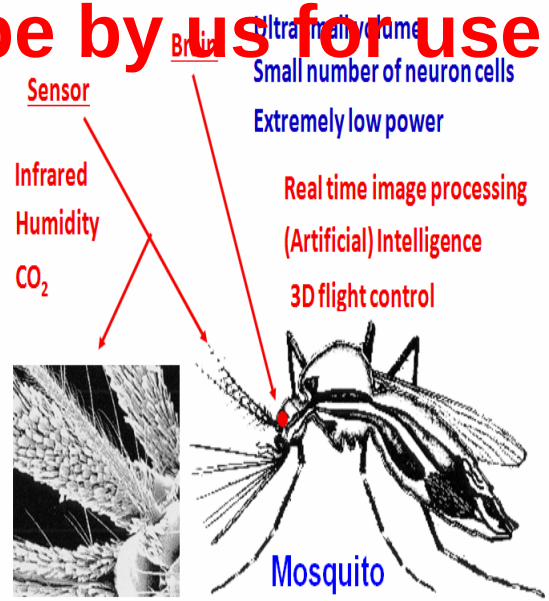
Scaling proceeds

Saturation of Downsizing

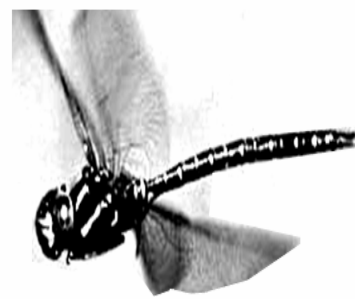
We do not know how?

Some time in 2020 - 2030

After 2050?



Dragonfly brain has even further higher performance



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Thank you
for your attention!